Data Sheet: Technical Data

MKW41Z512 Rev. 1, 10/2016

MKW41Z/31Z/21Z Data Sheet

A Bluetooth® Low Energy, IEEE® Standard 802.15.4, Generic FSK System on a Chip (SoC) Supports the following: MKW41Z512VHT4, MKW31Z512VHT4, MKW21Z512VHT4, MKW41Z256VHT4, MKW31Z256VHT4, MKW21Z256VHT4

MKW41Z512 MKW31Z512 MKW21Z512 MKW41Z256 MKW31Z256 MKW21Z256

Multi-Standard Radio

- 2.4 GHz Bluetooth Low Energy ver. 4.2 compliant supporting up to 2 simultaneous hardware connections
- IEEE Std. 802.15.4 compliant with dual-PAN support
- Generic FSK modulation
 - Data Rate: 250, 500 and 1000 kbps
 - Modulations: GFSK BT = 0.3, 0.5, 0.7; FSK/MSK
 - Modulation Index: 0.32, 0.5, or 0.7
- Typical Receiver Sensitivity (BLE) = -95 dBm
- Typical Receiver Sensitivity (802.15.4) = -100 dBm
- Typical Receiver Sensitivity (250 kbps GFSK-BT=0.5, h=0.5) = -100 dBm
- Prog Transmitter Output Power: -30 dBm to 3.5 dBm
- Low external component counts for low cost application
- · On-chip balun with single ended bidirectional RF port

MCU and Memories

- Up to 48 MHz ARM® Cortex-M0+ core
- On-chip 512/256 KB Flash memory
- On-chip 128/64 KB SRAM

Low Power Consumption

- Transceiver current (DC-DC buck mode, 3.6 V supply)
 - Typical Rx Current: 6.8 mA
 - Typical Tx current: 6.1 mA (0 dBm output)
- Low Power Mode (VLLS0) Current: 182 nA

Clocks

- 26 and 32 MHz supported for BLE and FSK modes
- 32 MHz supported for IEEE Standard 802.15.4
- · 32.768 kHz Crystal Oscillator

Operating Characteristics

- Voltage range: 0.9 V to 4.2 V
- Temperature range: -40 to 105 °C

Human-machine interface

- · Touch sensing input
- General-purpose input/output

System peripherals

- Nine MCU low-power modes to provide power optimization based on application requirements
- DC-DC Converter supporting Buck, Boost, and Bypass operating modes
- Direct memory access(DMA) Controller
- Computer operating properly(COP) watchdog
- Serial wire debug(SWD) Interface and Micro Trace buffer
- Bit Manipulation Engine (BME)

Analog Modules

- 16-bit Analog-to-Digital Converter (ADC)
- 12-bit Digital-to-Analog Converter (DAC)
- 6-bit High Speed Analog Comparator (CMP)
- 1.2 V voltage reference (VREF)

Timers

- 16-bit low-power timer (LPTMR)
- 3 Timers Modules(TPM): One 4 channel TPM and two 2 channel TPMs
- Programmable Interrupt Timer (PIT)
- Real-Time Clock (RTC)

Communication interfaces

- 2 serial peripheral interface (SPI) modules
- 2 inter-integrated circuit (I2C) modules
- Low Power UART module
- Carrier Modulator Timer (CMT)

Security

- AES-128 Hardware Accelerator (AESA)
- True Random Number Generator (TRNG)
- · Advanced flash security
- 80-bit unique identification number per chip
- 40-bit unique media access control (MAC) subaddress
- Bluetooth-LE v4.2 Secure Connections
- IEEE Standard 802.15.4-2011 compliant security



Table of Contents

1	Intro	duction.		3		7.3	Switch	ning electrical specifications	45
2	Orde	ring Info	ormation	4			7.3.1	Device clock specifications	45
3	Feat	ure Des	criptions	4			7.3.2	General switching specifications	46
	3.1	Block	Diagram	4		7.4	Therm	nal specifications	47
	3.2	Radio	features	5			7.4.1	Thermal operating requirements	47
	3.3	Micro	controller features	6			7.4.2	Thermal attributes	47
	3.4	Syster	n features	7		7.5	Periph	neral operating requirements and behaviors	48
	3.5	Periph	eral features	10			7.5.1	Core modules	48
	3.6	Securi	ty Features	14			7.5.2	System modules	49
4	Tran	sceiver	Description	16			7.5.3	Clock modules	49
	4.1	Key S	pecifications	16			7.5.4	Memories and memory interfaces	52
	4.2	Chann	el Map Frequency Plans	17			7.5.5	Security and integrity modules	54
		4.2.1	Channel Plan for Bluetooth Low Energy	17			7.5.6	Analog	54
		4.2.2	Channel Plan for IEEE 802.15.4 in 2.4GHz				7.5.7	Timers	65
			ISM and MBAN frequency bands	18			7.5.8	Communication interfaces	65
		4.2.3	Other Channel Plans	19			7.5.9	Human-machine interfaces (HMI)	70
	4.3	Transo	ceiver Functions	20	8	KW4	1Z Elec	ctrical Characteristics	71
5	Tran	sceiver	Electrical Characteristics	20		8.1	DC-D	C Converter Recommended Electrical	
	5.1	Recon	nmended radio operating conditions	20			Chara	cteristics	71
	5.2	Receiv	ver Feature Summary	21		8.2	Rating	gs	73
	5.3	Transr	mit and PLL Feature Summary	24			8.2.1	Thermal handling ratings	73
6	Syste	em and	Power Management	27			8.2.2	Moisture handling ratings	73
	6.1	Power	Management	27			8.2.3	ESD handling ratings	73
		6.1.1	DC-DC Converter	28			8.2.4	Voltage and current operating ratings	74
	6.2	Modes	of Operation	28	9	Pin [Diagram	ns and Pin Assignments	74
		6.2.1	Power modes	28		9.1	Pinou	ts	74
7	MCL	Electri	cal Characteristics	31		9.2	Signa	Multiplexing and Pin Assignments	75
	7.1	AC ele	ectrical characteristics	31		9.3	Modul	e Signal Description Tables	78
	7.2	Nonsy	vitching electrical specifications	31			9.3.1	Core Modules	79
		7.2.1	Voltage and current operating requirements	s 31			9.3.2	Radio Modules	79
		7.2.2	LVD and POR operating requirements	32			9.3.3	System Modules	80
		7.2.3	Voltage and current operating behaviors	33			9.3.4	Clock Modules	81
		7.2.4	Power mode transition operating behaviors	34			9.3.5	Analog Modules	81
		7.2.5	Power consumption operating behaviors	35			9.3.6	Timer Modules	82
		7.2.6	Diagram: Typical IDD_RUN operating				9.3.7	Communication Interfaces	83
			behavior	42			9.3.8	Human-Machine Interfaces(HMI)	84
		7.2.7	SoC Power Consumption	44	10	Pack	age Inf	ormation	84
		7.2.8	Designing with radiated emissions in mind.	45		10.1	Obtair	ning package dimensions	85
		7.2.9	Capacitance attributes	45	11	Revi	sion His	story	85

1 Introduction

The KW41Z/31Z/21Z (called KW41Z throughout this document) is an ultra low-power, highly integrated single-chip device that enables Bluetooth low energy (BLE), Generic FSK (at 250, 500 and 1000 kbps) or IEEE Standard 802.15.4 RF connectivity for portable, extremely low-power embedded systems. Applications include portable health care devices, wearable sports and fitness devices, AV remote controls, computer keyboards and mice, gaming controllers, access control, security systems, smart energy and home area networks.

The KW41Z SoC integrates a radio transceiver operating in the 2.36 GHz to 2.48 GHz range supporting a range of FSK/GFSK and O-QPSK modulations, an ARM Cortex-M0+ CPU, up to 512 KB Flash and up to 128 KB SRAM, BLE Link Layer hardware, 802.15.4 packet processor hardware and peripherals optimized to meet the requirements of the target applications.

The KW41Z SoC's radio frequency transceiver is compliant with Bluetooth version 4.2 for Low Energy (aka Bluetooth Smart or BLE), Generic FSK and the IEEE Standard 802.15.4 using O-QPSK in the 2.4 GHz ISM band. NXP provides fully certified Bluetooth Low Energy and IEEE Standard 802.15.4 protocol stacks, including Thread, and application profiles to support KW41Z.

The KW41Z SoC can be used in applications as a "BlackBox" modem by simply adding BLE or IEEE Standard 802.15.4 connectivity to an existing embedded controller system, or used as a stand-alone smart wireless sensor with embedded application where no host controller is required.

KW41Z has 512/256 KB of on-chip Flash and 128/64 KB of on-chip SRAM memory available to be used by customer applications and chosen communication protocol stack using a choice of either NXP or 3rd party software development tools.

The RF section of the KW41Z SoC is optimized to require very few external components, achieving the smallest RF footprint possible on a printed circuit board.

Extremely long battery life is achieved though efficiency of code execution in the Cortex-M0+ CPU core and the multiple low power operating modes of the KW41Z SoC. Additionally, an integrated DC-DC converter enables a wide operating range from 0.9 V to 4.2 V. The DC-DC in Buck mode enables KW41Z to operate from a single coin cell battery with a significant reduction of peak Rx and Tx current consumption. The DC-DC in boost mode enables a single alkaline battery to be used throughout its entire useful voltage range of 0.9 V to 1.795 V.

2 Ordering Information

Table 1. Orderable parts details

Device	Memory Configuration	Package	Description
MKW21Z512VHT4(R)	512 KB Flash, 128 KB SRAM	48-pin Laminate QFN	IEEE 802.15.4
MKW21Z256VHT4(R)	256 KB Flash, 64 KB SRAM		
MKW31Z512VHT4(R)	512 KB Flash, 128 KB SRAM	48-pin Laminate QFN	Bluetooth Low Energy and Generic FSK
MKW31Z256VHT4(R)	256 KB Flash, 64 KB SRAM		
MKW41Z512VHT4(R)	512 KB Flash, 128 KB SRAM	48-pin Laminate QFN	Bluetooth Low Energy and IEEE 802.15.4 and Generic FSK
MKW41Z256VHT4(R)	256 KB Flash, 64 KB SRAM		

3 Feature Descriptions

This section provides a simplified block diagram and highlights the KW41Z SoC features.

3.1 Block Diagram

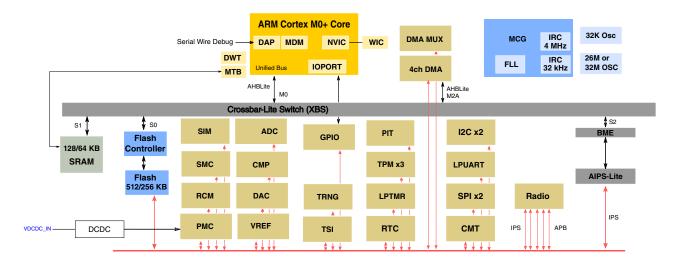


Figure 1. KW41Z Detailed Block Diagram

3.2 Radio features

Operating frequencies:

- 2.4 GHz ISM band (2400-2483.5 MHz)
- MBAN 2360-2400 MHz

Supported standards:

- Bluetooth v4.2 Low Energy compliant 1 Mbps GFSK modulation supporting up to 2 simultaneous connections in hardware (master-slave, master-master, slave-slave)
- IEEE Standard 802.15.4-2011 compliant O-QPSK modulation and security features
- Kinetis Thread Networking Stack
- Bluetooth Low Energy(BLE) Application Profiles

Receiver performance:

- Receive sensitivity of -95 dBm for BLE
- Receive sensitivity of -100 dBm typical for IEEE Standard 802.15.4
- Receive sensitivity of up to -100 dBm for a 250 kbps GFSK mode with a modulation index of 0.5. Receive sensitivity in generic FSK modes depends on mode selection and data rate.

Other features:

- Programmable transmit output power from -30 dBm to 3.5 dBm
- Integrated on-chip balun
- Single ended bidirectional RF port shared by transmit and receive
- Low external component count
- Supports transceiver range extension using external PA and/or LNA
- 26 and 32 MHz supported for BLE and FSK modes
- 32 MHz supported for IEEE Standard 802.15.4
- Bluetooth Low Energy ver. 4.2 Link Layer hardware with 2 independent hardware connection engines
- Hardware acceleration for IEEE Standard 802.15.4 packet processing/link layer
- Hardware acceleration for Generic FSK packet processing
- Supports dual PAN for IEEE Standard 802.15.4 with hardware-assisted address matching acceleration
- Generic FSK modulation at 250, 500 and 1000 kbps
- Supports antenna diversity option for IEEE Std. 802.15.4

3.3 Microcontroller features

ARM Cortex-M0+ CPU

- Up to 48 MHz CPU
- As compared to Cortex-M0, the Cortex-M0+ uses an optimized 2-stage pipeline microarchitecture for reduced power consumption and improved architectural performance (cycles per instruction)
- Supports up to 32 interrupt request sources
- Binary compatible instruction set architecture with the Cortex-M0 core
- Thumb instruction set combines high code density with 32-bit performance
- Serial Wire Debug (SWD) reduces the number of pins required for debugging
- Micro Trace Buffer (MTB) provides lightweight program trace capabilities using system RAM as the destination memory

Nested Vectored Interrupt Controller (NVIC)

- 32 vectored interrupts, 4 programmable priority levels
- Includes a single non-maskable interrupt

Wake-up Interrupt Controller (WIC)

• Supports interrupt handling when system clocking is disabled in low power modes

- Takes over and emulates the NVIC behavior when correctly primed by the NVIC on entry to very-deep-sleep
- A rudimentary interrupt masking system with no prioritization logic signals for wake-up as soon as a non-masked interrupt is detected

Debug Controller

- Two-wire Serial Wire Debug (SWD) interface
- Hardware breakpoint unit for 2 code addresses
- Hardware watchpoint unit for 2 data items
- Micro Trace Buffer for program tracing

On-Chip Memory

- 512/256 KB Flash
 - Firmware distribution protection. Flash can be marked execute-only on a persector (8 KB) basis to prevent firmware contents from being read by 3rd parties
 - Flash implemented as two equal blocks each of 256 KB block. Code can execute or read from one block while the other block is being erased or programmed
- 128/64 KB SRAM
- Security circuitry to prevent unauthorized access to RAM and flash contents through the debugger

3.4 System features

Power Management Control Unit (PMC)

- Programmable power saving modes
- Available wake-up from power saving modes via internal and external sources
- Integrated Power-on Reset (POR)
- Integrated Low Voltage Detect (LVD) with reset (brownout) capability
- Selectable LVD trip points
- Programmable Low Voltage Warning (LVW) interrupt capability
- Individual peripheral clocks can be gated off to reduce current consumption
- Internal Buffered bandgap reference voltage
- Factory programmed trim for bandgap and LVD
- 1 kHz Low Power Oscillator (LPO)

DC-DC Converters

- Internal switched mode power supply supporting Buck, Boost, and Bypass operating modes
- Buck operation supports external voltage sources of 2.1 V to 4.2 V. This reduces peak current consumption during Rx and Tx by ~25%, ideal for single coin-cell battery operation (typical CR2032 cell).
- Boost operation supports external voltage sources of 0.9 V to 1.795 V, which is efficiently increased to the static internal core voltage level, ideal for single battery operation (typical AA or AAA alkaline cell).
- When DC-DC is not used, the device supports an external voltage range of 1.5 V to 3.6 V (1.5 3.6 V on VDD_RF1, VDD_RF2, VDD_XTAL and VDD_1P5OUT_PMCIN pins. 1.71 3.6 V on VDD_0, VDD_1 and VDDA pins)
- An external inductor is required to support the Buck or Boost modes
- The DC-DC Converter 1.8 V output current drive for external devices (MCU in RUN mode, Radio is enabled, other peripherals are disabled)
 - Up to 44 mA in buck mode with VDD_1P8 = 1.8 V
 - Up to 31.4 mA in buck mode with VDD_1P8 = 3.0 V

Direct Memory Access (DMA) Controller

- All data movement via dual-address transfers: read from source, write to destination
- Programmable source and destination addresses and transfer size
- Support for enhanced addressing modes
- 4-channel implementation that performs complex data transfers with minimal intervention from a host processor
- Internal data buffer, used as temporary storage to support 16- and 32-byte transfers
- Connections to the crossbar switch for bus mastering the data movement
- Transfer control descriptor (TCD) organized to support two-deep, nested transfer operations
- 32-byte TCD stored in local memory for each channel
- An inner data transfer loop defined by a minor byte transfer count
- An outer data transfer loop defined by a major iteration count
- Channel activation via one of three methods:
 - Explicit software initiation
 - Initiation via a channel-to-channel linking mechanism for continuous transfers
 - Peripheral-paced hardware requests, one per channel
- Fixed-priority and round-robin channel arbitration
- Channel completion reported via optional interrupt requests
- One interrupt per channel, optionally asserted at completion of major iteration count

- Optional error terminations per channel and logically summed together to form one error interrupt to the interrupt controller
- Optional support for scatter/gather DMA processing
- Support for complex data structures

DMA Channel Multiplexer (DMA MUX)

- 4 independently selectable DMA channel routers
- 2 periodic trigger sources available
- Each channel router can be assigned to 1 of the peripheral DMA sources

COP Watchdog Module

- Independent clock source input (independent from CPU/bus clock)
- Choice between two clock sources
 - LPO oscillator
 - Bus clock

System Clocks

- Both 26 MHz and 32 MHz crystal reference oscillator supported for BLE and FSK radio modes
- 32 MHz crystal reference oscillator supported for IEEE 802.15.4 radio mode
- MCU can derive its clock either from the crystal reference oscillator or the frequency locked loop (FLL)¹
- 32/32.768 kHz crystal reference oscillator used to maintain precise Bluetooth radio time in low power modes
- Multipurpose Clock Generator (MCG)
- Internal reference clocks Can be used as a clock source for other on-chip peripherals
 - On-chip RC oscillator range of 31.25 kHz to 39.0625 kHz with 2% accuracy across full temperature range
 - On-chip 4MHz oscillator with 5% accuracy across full temperature range
- Frequency-locked loop (FLL) controlled by internal or external reference
 - 20 MHz to 48 MHz FLL output

Unique Identifiers

- 10 bytes(or 80-bits) of the Unique ID represents a unique identifier for each chip
- 40 bits of unique media access control (MAC) address, which can be used to build a unique 48-bit Bluetooth-LE or 64-bit IEEE 802.15.4 device address
 - 1. Clock options can have restrictions based on the chosen SoC configuration.

3.5 Peripheral features

16-bit Analog-to-Digital Converter (ADC)

- Linear successive approximation algorithm with 16-bit resolution
- Output formatted in differential-ended 16-, 13-, 11-, and 9-bit mode
- Output formatted in single-ended 16-, 12-, 10-, and 8-bit mode
- Single or continuous conversion
- Configurable sample time and conversion speed / power
- Conversion rates in 16-bit mode with no averaging up to ~500Ksamples/sec
- Input clock selection
- Operation in low power modes for lower noise operation
- Asynchronous clock source for lower noise operation
- Selectable asynchronous hardware conversion trigger
- Automatic compare with interrupt for less-than, or greater than, or equal to programmable value
- Temperature sensor
- Battery voltage measurement
- Hardware average function
- Selectable voltage reverence
- Self-calibration mode

12-Bit Digital-to-Analog Converter (DAC)

- 12-bit resolution
- Guaranteed 6-sigma monotonicity over input word
- High- and low-speed conversions
 - 1 µs conversion rate for high speed, 2 µs for low speed
- Power-down mode
- Automatic mode allows the DAC to generate its own output waveforms including square, triangle, and sawtooth
- Automatic mode allows programmable period, update rate, and range
- DMA support with configurable watermark level

High-Speed Analog Comparator (CMP)

- 6-bit DAC programmable reference generator output
- Up to eight selectable comparator inputs; each input can be compared with any input by any polarity sequence
- Selectable interrupt on rising edge, falling edge, or either rising or falling edges of comparator output

- Two performance modes:
 - Shorter propagation delay at the expense of higher power
 - Low power, with longer propagation delay
- Operational in all MCU power modes except VLLS0 mode

Voltage Reference(VREF1)

- Programmable trim register with 0.5 mV steps, automatically loaded with factory trimmed value upon reset
- Programmable buffer mode selection:
 - Off
 - Bandgap enabled/standby (output buffer disabled)
 - High power buffer mode (output buffer enabled)
- 1.2 V output at room temperature
- VREF_OUT output signal

Low Power Timer (LPTMR)

- One channel
- Operation as timer or pulse counter
- Selectable clock for prescaler/glitch filter
 - 1 kHz internal LPO
 - External low power crystal oscillator
 - Internal reference clock
- Configurable glitch filter or prescaler
- Interrupt generated on timer compare
- Hardware trigger generated on timer compare
- Functional in all power modes

Timer/PWM (TPM)

- TPM0: 4 channels, TPM1 and TPM2: 2 channels each
- Selectable source clock
- Programmable prescaler
- 16-bit counter supporting free-running or initial/final value, and counting is up or up-down
- Input capture, output compare, and edge-aligned and center-aligned PWM modes
- Input capture and output compare modes
- Generation of hardware triggers
- TPM1 and TPM2: Quadrature decoder with input filters
- Global time base mode shares single time base across multiple TPM instances

Programmable Interrupt Timer (PIT)

Feature Descriptions

- Up to 2 interrupt timers for triggering ADC conversions
- 32-bit counter resolution
- Clocked by bus clock frequency

Real-Time Clock (RTC)

- 32-bit seconds counter with 32-bit alarm
 - Can be invalidated on detection of tamper detect
- 16-bit prescaler with compensation
- Register write protection
 - Hard Lock requires MCU POR to enable write access
 - Soft lock requires POR or software reset to enable write/read access
- Capable of waking up the system from low power modes

Inter-Integrated Circuit (I²C)

- Two channels
- Compatible with I2C bus standard and SMBus Specification Version 2 features
- Up to 400 kHz operation
- Multi-master operation
- Software programmable for one of 64 different serial clock frequencies
- Programmable slave address and glitch input filter
- Interrupt driven byte-by-byte data transfer
- Arbitration lost interrupt with automatic mode switching from master to slave
- Calling address identification interrupt
- Bus busy detection broadcast and 10-bit address extension
- Address matching causes wake-up when processor is in low power mode

LPUART

- One channel
- Full-duplex operation
- Standard mark/space non-return-to-zero (NRZ) format
- 13-bit baud rate selection with fractional divide of 32
- Programmable 8-bit or 9-bit data format
- Programmable 1 or 2 stop bits
- Separately enabled transmitter and receiver
- Programmable transmitter output polarity
- Programmable receive input polarity
- 13-bit break character option
- 11-bit break character detection option
- Two receiver wakeup methods:

- Idle line wakeup
- Address mark wakeup
- Address match feature in receiver to reduce address mark wakeup ISR overhead
- Interrupt or DMA driven operation
- Receiver framing error detection
- Hardware parity generation and checking
- Configurable oversampling ratio to support from 1/4 to 1/32 bit-time noise detection
- Operation in low power modes
- Hardware Flow Control RTS\CTS
- Functional in Stop/VLPS modes

Serial Peripheral Interface (DSPI)

- Two independent SPI channels
- Master and slave mode
- Full-duplex, three-wire synchronous transfers
- Programmable transmit bit rate
- Double-buffered transmit and receive data registers
- Serial clock phase and polarity options
- Slave select output
- Control of SPI operation during wait mode
- Selectable MSB-first or LSB-first shifting
- Support for both transmit and receive by DMA

Carrier Modulator Timer (CMT)

- Four modes of operation
 - Time; with independent control of high and low times
 - Baseband
 - Frequency shift key (FSK)
 - Direct software control of CMT_IRO signal
- Extended space operation in time, baseband, and FSK modes
- Selectable input clock divider
- Interrupt on end of cycle
- Ability to disable CMT_IRO signal and use as timer interrupt

General Purpose Input/Output (GPIO)

- Hysteresis and configurable pull up device on all input pins
- Independent pin value register to read logic level on digital pin
- All GPIO pins can generate IRQ and wakeup events
- Configurable drive strength on some output pins

Touch Sensor Input (TSI)

- Support up to 16 external electrodes
- Automatic detection of electrode capacitance across all operational power modes
- Internal reference oscillator for high-accuracy measurement
- Configurable software or hardware scan trigger
- Capability to wake MCU from low power modes
- Compensate for temperature and supply voltage variations
- High sensitivity change with 16-bit resolution register
- Configurable up to 4096 scan times
- Support DMA data transfer

Keyboard Interface

- GPIO can be configured to function as a interrupt driven keyboard scanning matrix
 - In the 48pin package there are a total of 26 digital pins
 - These pins can be configured as needed by the application as GPIO, LPUART, SPI, I2C, ADC, timer I/O as well as other functions

3.6 Security Features

Advanced Encryption Standard Accelerator(AES-128 Accelerator)

The advanced encryption standard accelerator (AESA) module is a standalone hardware coprocessor capable of accelerating the 128-bit advanced encryption standard (AES) cryptographic algorithms.

The AESA engine supports the following cryptographic features.

LTC includes the following features:

- Cryptographic authentication
 - Message authentication codes (MAC)
 - Cipher-based MAC (AES-CMAC)
 - Extended cipher block chaining message authentication code (AES-XCBC-MAC)
 - Auto padding
 - Integrity Check Value(ICV) checking
- Authenticated encryption algorithms
 - Counter with CBC-MAC (AES-CCM)
 - Galois counter mode (AES-GCM)
- Symmetric key block ciphers

- AES (128-bit keys)
- Cipher modes:
 - AES-128 modes
 - Electronic codebook (ECB)
 - Cipher block chaining (CBC)
 - Counter (CTR)
 - DES modes
 - Electronic codebook (ECB)
 - Cipher block chaining (CBC)
 - Cipher feedback (CFB)
 - Output Feedback (OFB)
- Secure scan

True Random Number Generator (TRNG)

True Random Number Generator (TRNG) is a hardware accelerator module that constitutes a high-quality entropy source.

- TRNG generates a 512-bit (4x 128-bit) entropy as needed by an entropy-consuming module., such as a deterministic random number generator.
- TRNG output can be read and used by a deterministic pseudo-random number generator (PRNG) implemented in software.
- TRNG-PRNG combination achieves NIST compliant true randomness and cryptographic-strength random numbers using the TRNG output as the entropy source.
- A fully FIPS 180 compliant solution can be realized using the TRNG together with a FIPS compliant deterministic random number generator and the SoC-level security.

Flash Memory Protection

The on-chip flash memory controller enables the following useful features:

- Program flash protection scheme prevents accidental program or erase of stored data.
- Program flash access control scheme prevents unauthorized access to selected code segments.
- Automated, built-in, program and erase algorithms with verify.
- Read access to one program flash block is possible while programming or erasing data in the other program flash block.

4 Transceiver Description

- Direct Conversion Receiver
- Constant Envelope Transmitter
- 2.36 GHz to 2.483 GHz PLL Range
- Low Transmit and Receive Current Consumption
- Low BOM

4.1 Key Specifications

The KW41Z SoC meets or exceeds all Bluetooth Low Energy v4.2 and IEEE 802.15.4 performance specifications applicable to 2.4 GHz ISM and MBAN (Medical Band Area Network) bands. Key specification for the KW41 are:

Frequency Band:

ISM Band: 2400 to 2483.5MHzMBAN Band: 2360 to 2400MHz

Bluetooth Low Energy v4.2 modulation scheme:

• Symbol rate: 1000 kbps

• Modulation: GFSK

• Receiver sensitivity: -95 dBm, typical

• Programmable transmitter output power: -30 dBm to 3.5 dBm

IEEE Standard 802.15.4 2.4 GHz modulation scheme:

• Chip rate: 2000 kbps

• Data rate: 250 kbps

• Symbol rate: 62.5 kbps

• Modulation: OQPSK

• Receiver sensitivity: -100 dBm, typical (@1% PER for 20 byte payload packet)

• Single ended bidirectional RF input/output port with integrated transmit/receive switch

• Programmable transmitter output power: -30 dBm to 3.5 dBm

Generic FSK modulation scheme:

• Symbol rate: 250, 500 and 1000 kbps

- Modulation(s): GFSK (modulation index = 0.32, 0.5, and 0.7, BT =0.5, 0.3 and 0.7), MSK
- Receiver Sensitivity: Mode and data rate dependant. -100 dBm typical for GFSK (r=250 kbps, BT = 0.5, h = 0.5)

4.2 Channel Map Frequency Plans

4.2.1 Channel Plan for Bluetooth Low Energy

This section describes the frequency plan / channels associated with 2.4GHz ISM and MBAN bands for Bluetooth Low Energy.

2.4GHz ISM Channel numbering:

• Fc=2402 + k * 2 MHz, k=0,...,39.

MBAN Channel numbering:

- Fc=2363 + 5*k in MHz, for k=0,....,6
- Fc=2367 + 5*(k-7) in MHz, for k=7,8....,13)

where k is the channel number.

Table 2. 2.4 GHz ISM and MBAN frequency plan and channel designations

2.4 GI	Hz ISM ¹	МВ	AN ²	2.4GHz ISM + MBAN		
Channel	Freq (MHz)	Channel Freq (MHz)		Channel	Freq (MHz)	
0	2402	0	2360	28	2390	
1	2404	1	2361	29	2391	
2	2406	2	2362	30	2392	
3	2408	3	2363	31	2393	
4	2410	4	2364	32	2394	
5	2412	5	2365	33	2395	
6	2414	6	2366	34	2396	
7	2416	7	2367	35	2397	
8	2418	8	2368	36	2398	
9	2420	9	2369	0	2402	
10	2422	10	2370	1	2404	

Table 2. 2.4 GHz ISM and MBAN frequency plan and channel designations (continued)

2.4 G	Hz ISM ¹	MB	AN ²	2.4GHz ISI	M + MBAN
Channel	Freq (MHz)	Channel	Freq (MHz)	Channel	Freq (MHz)
11	2424	11	2371	2	2406
12	2426	12	2372	3	2408
13	2428	13	2373	4	2410
14	2430	14	2374	5	2412
15	2432	15	2375	6	2414
16	2434	16	2376	7	2416
17	2436	17	2377	8	2418
18	2438	18	2378	9	2420
19	2440	19	2379	10	2422
20	2442	20	2380	11	2424
21	2444	21	2381	12	2426
22	2446	22	2382	13	2428
23	2448	23	2383	14	2430
24	2450	24	2384	15	2432
25	2452	25	2385	16	2434
26	2454	26	2386	17	2436
27	2456	27	2387	18	2438
28	2458	28	2388	19	2440
29	2460	29	2389	20	2442
30	2462	30	2390	21	2444
31	2464	31	2391	22	2446
32	2466	32	2392	23	2448
33	2468	33	2393	24	2450
34	2470	34	2394	25	2452
35	2472	35	2395	26	2454
36	2474	36	2396	27	2456
37	2476	37	2397	37	2476
38	2478	38	2398	38	2478
39	2480	39	2399	39	2480
	1	l		1	

^{1.} ISM frequency of operation spans from 2400.0 MHz to 2483.5 MHz

^{2.} Per FCC guideline rules, IEEE (R) 802.15.1 and Bluetooth Low Energy single mode operation is allowed in these channels.

4.2.2 Channel Plan for IEEE 802.15.4 in 2.4GHz ISM and MBAN frequency bands

This section describes the frequency plan / channels associated with 2.4GHz ISM and MBAN bands for IEEE 802.15.4.

2.4GHz ISM Channel numbering:

• Fc=2405 + 5*(k-11) MHz, k=11, 12, ..., 26.

MBAN Channel numbering:

- Fc=2363.0 + 5*k in MHz, for k=0,....,6
- Fc=2367.0 + 5*(k-7) in MHz, for k=7,....,14

where k is the channel number.

Table 3. 2.4 GHz ISM and MBAN frequency plan and channel designations

2.4 (GHz ISM	M	IBAN ¹
Channel #	Frequency (MHz)	Channel #	Frequency (MHz)
11	2405	0	2363
12	2410	1	2368
13	2415	2	2373
14	2420	3	2378
15	2425	4	2383
16	2430	5	2388
17	2435	6	2393
18	2440	7	2367
19	2445	8	2372
20	2450	9	2377
21	2455	10	2382
22	2460	11	2387
23	2465	12	2392
24	2470	13	2397
25	2475	14	2395
26	2480		

^{1.} Usable channel spacing to assit in co-existence.

4.2.3 Other Channel Plans

The RF synthesizer can be configured to use any channel frequency between 2.36 and 2.487 GHz.

4.3 Transceiver Functions

Receive

The receiver architecture is Zero IF (ZIF) where the received signal after passing through RF front end is down-converted to a baseband signal. The signal is filtered and amplified before it is fed to analog-to-digital converter. The digital signal is then decimated to a baseband clock frequency before it is digitally processed, demodulated and passed on to packet processing/link-layer processing.

Transmit

The transmitter transmits O-QPSK or GFSK/FSK modulation having power and channel selection adjustment per user application. After the channel of operation is determined, coarse and fine tuning is executed within the Frac-N PLL to engage signal lock. After signal lock is established, the modulated buffered signal is then routed to a multi-stage amplifier for transmission. The differential signals at the output of the PA (RF_P, RF_N) are converted to a single ended(SE) output signal by an on-chip balun.

5 Transceiver Electrical Characteristics

5.1 Recommended radio operating conditions

Table 4. Recommended operating conditions

Characteristic	Symbol	Min	Тур	Max	Unit
Bypass Mode RF and Analog Power Supply Voltage	VDD _{RF1} , VDD _{RF2} , VDD _{RF3}	1.425	1.5	3.6	Vdc
Bypass Mode Supply Voltage (Digital)	$VDD_X, V_{DCDC_IN}, VDD_A$	1.71	_	3.6	Vdc
Boost Mode Supply Voltage	VDD _{DCDC_IN}	0.9	_	1.795	Vdc
Buck Mode Supply Voltage ^{2, 1}	VDD _{DCDC_IN}	2.1	_	4.2	Vdc

Table 4. Recommended operating conditions (continued)

Characteristic	Symbol	Min	Тур	Max	Unit
Input Frequency	fin	2.360	_	2.480	GHz
Ambient Temperature Range	TA	-40	25	105	°C
Logic Input Voltage Low	VIL	0	_	30% VDD _{INT}	V
Logic Input Voltage High	VIH	70% VDD _{INT}	_	VDD _{INT}	V
SPI Clock Rate	f _{SPI}	_	_	12.0	MHz
RF Input Power	Pmax	_	_	10	dBm
Crystal Reference Oscillator Frequency (±40 ppm over operating conditions to meet the 802.15.4 Standard.)	fref		26 MHz (or 32 MHz	

In Buck and Boost modes, DCDC converter will generate 1.8 V at VDD_1P8OUT and 1.5 V at VDD_1P5OUT_PMCIN pins. VDD_1P8OUT should supply to VDD₁, VDD₂ and VDD_A. VDD_1P5OUT_PMCIN should supply to VDD_RF₁ and VDD_RF₂. VDD_{XTAL} can be either supplied by 1.5 V or 1.8 V

5.2 Receiver Feature Summary

Table 5. Top Level Receiver Specifications (TA=25°C, nominal process unless otherwise noted)

Characteristic ¹	Symbol	Min.	Тур.	Max.	Unit
Supply current power down on VDD_RFx supplies	I _{pdn}	_	200	1000	nA
Supply current Rx On with DC-DC converter enable (Buck; VDD _{DCDC_in} = 3.6 V) , ²	I _{Rxon}	_	6.76	_	mA
Supply current Rx On with DC-DC converter disabled (Bypass) ²	I _{Rxon}	_	16.2	_	mA
Input RF Frequency	f _{in}	2.360	_	2.4835	GHz
GFSK Rx Sensitivity(250 kbps GFSK-BT=0.5, h=0.5)	SENS _{GFSK}	_	-100	_	dBm
BLE Rx Sensitivity ³	SENS _{BLE}	_	-95	_	dBm
IEEE 802.15.4 Rx Sensitivity ⁴	SENS _{15.4}		-100	_	dBm
Noise Figure for max gain mode @ typical sensitivity	NF _{HG}	_	7.5	_	dB
Receiver Signal Strength Indicator Range ⁵	RSSI _{Range}	-100	_	5	dBm
Receiver Signal Strength Indicator Resolution	RSSI _{Res}		1	_	dBm
Typical RSSI variation over frequency		-2	_	2	dB
Typical RSSI variation over temperature		-2	_	2	dB
Narrowband RSSI accuracy ⁶	RSSI _{Acc}	-3	_	3	dB
BLE Co-channel Interference (Wanted signal at -67 dBm , BER <0.1%. Measurement resolution 1 MHz).	BLE _{co-channel}		-7		dB

^{2.} In Buck mode, DCDC converter needs 2.1 V min to start, the supply can drop to 1.8 V after DCDC converter settles.

^{3.} VDD_{INT} is the internal LDO regulated voltage supplying various circuit blocks, VDD_{INT}=1.2 V

Table 5. Top Level Receiver Specifications (TA=25°C, nominal process unless otherwise noted) (continued)

Characteristic ¹	Symbol	Min.	Тур.	Max.	Unit
IEEE 802.15.4 Co-channel Interference (Wanted signal 3 dB over reference sensitivity level)	15.4 _{co-channel}	_	-2		dB
Adjacent/Alternate Channel Performance ⁷		'	•	'	
BLE Adjacent +/- 1 MHz Interference offset (Wanted signal at -67 dBm , BER <0.1%. Measurement resolution 1 MHz.)	SEL _{BLE, 1 MHz}	_	2	_	dB
BLE Adjacent +/- 2 MHz Interference offset (Wanted signal at -67 dBm , BER <0.1%. Measurement resolution 1 MHz.)	SEL _{BLE, 2 MHz}	_	40	_	dB
BLE Alternate ≥ +/-3 MHz Interference offset (Wanted signal at -67 dBm, BER <0.1%. Measurement resolution 1 MHz.)	SEL _{BLE} , 3 MHz	_	50	_	dB
IEEE 802.15.4 Adjacent +/- 5 MHz Interference offset (Wanted signal 3 dB over reference sensitivity level , PER <1%)	SEL _{15.4,5 MHz}	_	45	_	dB
IEEE 802.15.4 Alternate ≥ +/- 10 MHz Interference offset (Wanted signal 3 dB over reference sensitivity level , PER <1%.)	SEL _{15.4,5 MHz}	_	60	_	dB
Intermodulation Performance		•			
BLE Intermodulation with continuous wave interferer at ± 3MHz and modulated interferer is at ± 6MHz (Wanted signal at -67 dBm , BER<0.1%.)		_	-42	_	dBm
BLE Intermodulation with continuous wave interferer at ±5MHz and modulated interferer is at ±10MHz (Wanted signal at -67 dBm , BER<0.1%.)		_	-35	_	dBm
Blocking Performance ⁷		·	I	1	
BLE Out of band blocking from 30 MHz to 1000 MHz and 4000 MHz to 5000 MHz (Wanted signal at -67 dBm , BER<0.1%. Interferer continuous wave signal.) ⁸	_	_	-5	_	dBm
BLE Out of band blocking from 1000 MHz to 2000 MHz and 3000 MHz to 4000MHz (Wanted signal at -67 dBm , BER<0.1%. Interferer continuous wave signal.)	_	_	-12	_	dBm
BLE Out of band blocking from 2001 MHz to 2339MHz and 2484 MHz to 2999 MHz (Wanted signal at -67 dBm , BER<0.1%. Interferer continuous wave signal.)	_	_	-20	_	dBm
BLE Out of band blocking from 5000 MHz to 12750 MHz (Wanted signal at -67 dBm , BER<0.1%. Interferer continuous wave signal.) ⁸	_	_	0	_	dBm
IEEE 802.15.4 Out of band blocking for frequency offsets > 10 MHz and <= 80 MHz(Wanted signal 3 dB over reference sensitivity level , PER <1%. Interferer continuous wave signal.) ⁹		_	-36	_	dBm
IEEE 802.15.4 Out of band blocking from carrier frequencies in 1GHz to 4GHz range excluding frequency offsets < ±80 MHz (Wanted signal 3 dB over		_	-25	_	dBm

Table 5. Top Level Receiver Specifications (TA=25°C, nominal process unless otherwise noted) (continued)

Characteristic ¹	Symbol	Min.	Тур.	Max.	Unit
reference sensitivity level , PER <1%. Interferer continuous wave signal.)					
IEEE 802.15.4 Out of band blocking frequency from carrier frequencies < 1 GHz and > 4 GHz (Wanted signal 3 dB over reference sensitivity level , PER <1%. Interferer continuous wave signal. ⁸		_	-15	_	dBm
Spurious Emission < 1.6 MHz offset (Measured with 100 kHz resolution and average detector. Device transmit on RF channel with center frequency fc and spurious power measured in 1 MHz at RF frequency f), where If-fcl< 1.6 MHz	_	_	-54	_	dBc
Spurious Emission > 2.5 MHz offset (Measured with 100 kHz resolution and average detector. Device transmit on RF channel with center frequency fc and spurious power measured in 1 MHz at RF frequency f), where If-fcl> 2.5 MHz ¹⁰	_	_	-70	_	dBc

- 1. All the RX parameters are measured at the KW41 RF pins
- 2. Transceiver power consumption
- 3. Measured at 0.1% BER using 37 byte long packets in max gain mode and nominal conditions
- 4. In max gain mode and nominal conditions
- 5. RSSI performance in narrowband mode
- 6. With one point calibration over frequency and temperature
- 7. BLE Adjacent and Block parameters are measured with modulated interference signals
- 8. Exceptions allowed for carrier frequency harmonics.
- 9. Exception to the 10 MHz > freq offset <= 80 MHz out-of-band blocking limit allowed for frequency offsets of twice the reference frequency(fref).
- 10. Exceptions allowed for twice the reference clock frequency(fref) multiples.

Table 6. Receiver Specifications with Generic FSK Modulations

					Adjacent/	Alternate C	hannel Sele	ctivity (dB)	I
Modulation Type	Data Rate (kbps)	Channel BW (kHz)	Typical Sensitivity (dBm)	Desired signal level (dBm)	Interferer at -/+1* channel BW offset	Interferer at -/+ 2* channel BW offset	Interferer at -/+ 3* channel BW offset	Interferer at -/+ 4* channel BW offset	Co- channel
GFSK BT =	1000	2000	-95	67	45	50	52	52	-7
0.5, h=0.5	500	1000	-97	85	33	44	49	51	-7
	250	500	-100	85	20	33	42	46	-7
GFSK, BT =	1000	1000	-89	67	30	36	41	42	-7
0.5, h=0.3	500	800	-91	85	25	36	37	43	-13
	250	500	-93	85	25	25	37	37	-13
GFSK, BT =	1000	2000	-96	85	35	45	50	55	-7
0.5, h=0.7	500	1000	-98	85	32	44	47	50	-7
	250	600	-99	85	30	34	46	45	-7

Table 6. Receiver Specifications with Generic FSK Modulations (continued)

					Adjacent/	Alternate C	hannel Sele	ctivity (dB)	I
Modulation Type	Data Rate (kbps)	Channel BW (kHz)	Typical Sensitivity (dBm)	Desired signal level (dBm)	Interferer at -/+1* channel BW offset	Interferer at -/+ 2* channel BW offset	Interferer at -/+ 3* channel BW offset	Interferer at -/+ 4* channel BW offset	Co- channel
GMSK	1000	1600	-91	85	35	40	45	50	-8
BT=0.3	500	800	-93	85	30	40	40	45	-7
	250	500	-95	85	20	32	32	40	-7
GMSK, BT =	1000	2000	-96	85	35	45	50	55	-7
0.7	500	1000	-97	85	30	45	48	50	-7
	250	600	-99	85	30	33	45	45	-7
Generic	1000	3000	-96	85	39	50	58	63	-7
MSK	500	1600	-98	85	38	47	50	55	-7
	250	800	-99	85	30	46	45	50	-7

^{1.} Selectivity measured with an unmodulated blocker

5.3 Transmit and PLL Feature Summary

- Supports constant envelope modulation of 2.4 GHz ISM and 2.36 GHz MBAN frequency bands
- Fast PLL Lock time: $< 25 \mu s$
- Reference Frequency:
 - 26 and 32 MHz supported for BLE and FSK modes
 - 32 MHz supported for IEEE Standard 802.15.4

Table 7. Top level Transmitter Specifications (TA=25°C, nominal process unless otherwise noted)

Characteristic ¹	Symbol	Min.	Тур.	Max.	Unit
Supply current power down on VDD_RFx supplies	I _{pdn}	_	200	_	nA
Supply current Tx On with P _{RF} = 0dBm and DC-DC converter enabled (Buck; VDD _{DCDC_in} = 3.6 V), ²	I _{Txone}	_	6.08	_	mA
Supply current Tx On with P _{RF} = 0 dBm and DC-DC converter disabled (Bypass) ²	I _{Txond}	_	14.7	_	mA
Output Frequency	f _c	2.360	_	2.4835	GHz
Maximum RF Output power ³	P _{RF,max}		3.5	_	dBm
Minimum RF Output power ³	P _{RF,min}	_	-30	_	dBm
RF Output power control range	P _{RFCR}	_	34	_	dB

Table 7. Top level Transmitter Specifications (TA=25°C, nominal process unless otherwise noted) (continued)

Characteristic ¹	Symbol	Min.	Тур.	Max.	Unit
IEEE 802.15.4 Peak Frequency Deviation	F _{dev15.4}	_	±500	_	kHz
IEEE 802.15.4 Error Vector Magnitude ⁴	EVM _{15.4}		4.5	8	%
IEEE 802.15.4 Offset Error Vector Magnitude ⁵	OEVM _{15.4}		0.5	2	%
IEEE 802.15.4 TX spectrum level at 3.5MHz offset ^{4, 6}	TXPSD _{15.4}			-40	dBc
BLE TX Output Spectrum 20dB BW	TXBW _{BLE}	1.0		_	MHz
BLE average frequency deviation using a 00001111 modulation sequence	Δf1 _{avg,BLE}		250		kHz
BLE average frequency deviation using a 01010101 modulation sequence	Δf2 _{avg,BLE}		220		kHz
BLE RMS FSK Error	FSK _{err} , _{BLE}		3%		
BLE Maximum Deviation of the Center Frequency ⁷	F _{cdev,BLE}	_	±10	_	kHz
BLE Adjacent Channel Transmit Power at 2MHz offset ⁶	P _{RF2MHz,BLE}	_	_	-50	dBm
BLE Adjacent Channel Transmit Power at >= 3MHz offset ⁶	P _{RF3MHz,BLE}	_	_	-55	dBm
BLE Frequency Hopping Support			YES		
2 nd Harmonic of Transmit Carrier Frequency (Pout = PRF,max) ^{, 8}	TXH2	_	-46	_	dBm/MHz
3 rd Harmonic of Transmit Carrier Frequency (Pout = PRF,max) ⁸	TXH3	_	-58	_	dBm/MHz

- 1. All the TX parameters are measured at test hardware SMA connector
- 2. Transceiver power consumption
- 3. Measured at the KW41Z RF pins
- 4. Measured as per IEEE Standard 802.15.4
- 5. Offset EVM is computed at one point per symbol, by combining the I value from the beginning of each symbol and the Q value from the middle of each symbol into a single complex value for EVM computations
- 6. Measured at Pout = 5dBm and recommended TX match
- 7. Maximum drift of carrier frequency of the PLL during a BLE packet with a nominal 32MHz reference crystal
- 8. Harmonic Levels based on recommended 2 component match. Transmit harmonic levels depend on the tolerances and quality of the matching components.

Transmit PA driver output as a function of the PA_POWER[5:0] field when measured at the IC pins is as follows:

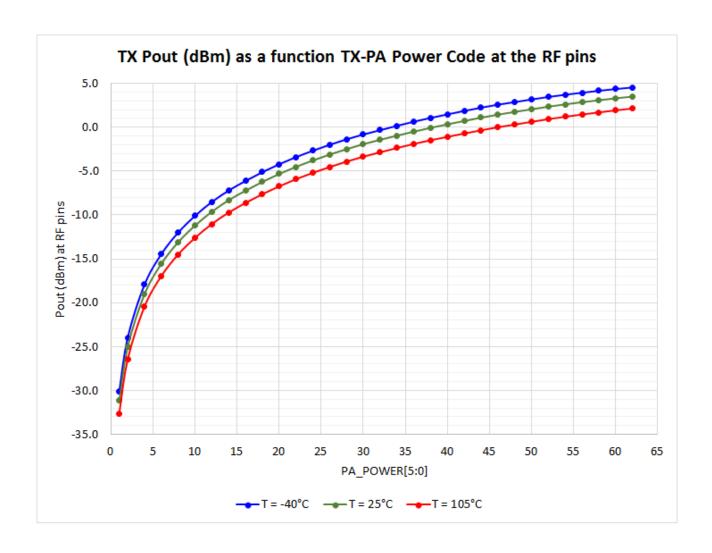


Table 8. Transmit Output Power as a function of PA_POWER[5:0]

		TX Pout (dBm)	
PA_POWER[5:0]	T = -40 °C	T = 25 °C	T = 105 °C
1	-30.1	-31.1	-32.6
2	-24.0	-25.0	-26.4
4	-17.9	-19.0	-20.4
6	-14.5	-15.6	-17.0
8	-12.0	-13.1	-14.5
10	-10.1	-11.2	-12.6
12	-8.5	-9.6	-11.0
14	-7.2	-8.3	-9.7
16	-6.1	-7.2	-8.6

Table 8. Transmit Output Power as a function of PA_POWER[5:0] (continued)

		TX Pout (dBm)	
PA_POWER[5:0]	T = -40 °C	T = 25 °C	T = 105 °C
18	-5.1	-6.2	-7.6
20	-4.2	-5.3	-6.7
22	-3.4	-4.5	-5.9
24	-2.7	-3.8	-5.2
26	-2.0	-3.1	-4.5
28	-1.4	-2.5	-3.9
30	-0.8	-1.9	-3.3
32	-0.3	-1.4	-2.8
34	0.2	-1.0	-2.4
36	0.6	-0.5	-1.9
38	1.1	-0.1	-1.5
40	1.5	0.3	-1.1
42	1.9	0.7	-0.7
44	2.2	1.1	-0.3
46	2.6	1.4	0.0
48	2.9	1.8	0.3
50	3.2	2.1	0.6
52	3.5	2.4	0.9
54	3.7	2.6	1.2
56	3.9	2.9	1.5
58	4.2	3.1	1.7
60	4.4	3.3	1.9
62	4.5	3.5	2.1

6 System and Power Management

6.1 Power Management

The KW41Z SoC includes internal power management features that can be used to control the power usage. The power management of the KW41Z includes power management controller (PMC) and a DC-DC converter which can operate in a buck, boost or bypass configuration. The PMC is designed such that the RF radio will

remain in state-retention while the core is in various stop modes. It can make sure the device can stay in low current consumption mode while the RF radio can wakeup quick enough for communication.

6.1.1 DC-DC Converter

The features of the DC-DC converter include the following:

- Single inductor, multiple outputs
- Buck and boost modes (pin selectable; CFG=VDCDC_IN -> buck; CFG=GND -> boost)
- Continuous or pulsed operation (hardware/software configurable)
- Power switch input to allow external control of power up, and to select bypass mode
- Output signal to indicate power stable. Purpose is for the rest of the chip to use as a POR
- Scaled battery output voltage suitable for SAR ADC utilization
- Internal oscillator for support when the reference oscillator is not present
- 1.8 V output is capable to supply external device: max 38.9 mA (V1P8 = 1.8 V, VDCDC_IN = 3.0 V) and 20.9 mA (V1P8 = 3.0 V, VDCDC_IN = 3.0 V), with MCU in RUN mode, peripherals are disabled.

6.2 Modes of Operation

The ARM Cortex-M0+ core in the KW41Z SoC has three primary modes of operation: Run, Wait, and Stop modes. For each run mode, there is a corresponding wait and stop mode. Wait modes are similar to ARM sleep modes. Stop modes are similar to ARM deep sleep modes. The very low power run (VLPR) operation mode can drastically reduce runtime power when the maximum bus frequency is not required to handle the application needs.

The WFI instruction invokes both wait and stop modes for KW41Z. The primary modes are augmented in a number of ways to provide lower power based on application needs.

6.2.1 Power modes

The power management controller (PMC) provides multiple power options to allow the user to optimize power consumption for the level of functionality needed.

Depending on the stop requirements of the user application, a variety of stop modes are available that provide state retention, partial power down or full power down of certain logic and/or memory. I/O states are held in all modes of operation. The following table compares the various power modes available.

For each run mode there is a corresponding wait and stop mode. Wait modes are similar to ARM sleep modes. Stop modes (VLPS, STOP) are similar to ARM sleep deep mode. The very low power run (VLPR) operating mode can drastically reduce runtime power when the maximum bus frequency is not required to handle the application needs.

The three primary modes of operation are run, wait and stop. The WFI instruction invokes either wait or stop depending on the SLEEPDEEP bit in Cortex-M0+ System Control Register. The primary modes are augmented in a number of ways to provide lower power based on application needs.

Table 9. Power modes (At 25 deg C)

Power mode	Description	CPU recovery method	Radio
Normal Run (all peripherals clock off)	Allows maximum performance of chip.	_	Radio can be active
Normal Wait - via WFI	Allows peripherals to function, while allowing CPU to go to sleep reducing power.	Interrupt	
Normal Stop - via WFI	Places chip in static state. Lowest power mode that retains all registers while maintaining LVD protection.	Interrupt	
PStop2 (Partial Stop 2)	Core and system clocks are gated. Bus clock remains active. Masters and slaves clocked by bus clock remain in Run or VLPRun mode. The clock generators in MCG and the on-chip regulator in the PMC also remain in Run or VLPRun mode.	Interrupt	
PStop1 (Partial Stop 1)	Core, system clocks and bus clock are gated. All bus masters and slaves enter Stop mode. The clock generators in MCG and the on-chip regulator in the PMC also remain in Run or VLPRun mode.	Interrupt	
VLPR (Very Low Power Run) (all peripherals off)	Reduced frequency (1MHz) Flash access mode, regulator in low power mode, LVD off. Internal oscillator can provide low power 4 MHz source for core. (Values @2MHz core/ 1MHz bus and flash, module off, execution from flash).	_	Radio operation is possible only when DC-DC is configured for continuous mode. However, there may be insufficient MIPS with a 4MHz MCU to support much
	Biasing is disabled when DC-DC is configured for continuous mode in VLPR/W		in the way of radio operation.
VLPW (Very Low Power Wait) - via WFI (all peripherals off)	Similar to VLPR, with CPU in sleep to further reduce power. (Values @4MHz core/ 1MHz bus, module off)	Interrupt	

Table 9. Power modes (At 25 deg C) (continued)

Power mode	Description	CPU recovery method	Radio
	Biasing is disabled when DC-DC is configured for continous mode in VLPR/W		
VLPS (Very Low Power Stop) via WFI	Places MCU in static state with LVD operation off. Lowest power mode with ADC and all pin interrupts functional. LPTMR, RTC, CMP, TSI can be operational.	Interrupt	
	Biasing is disabled when DC-DC is configured for continuous mode in VLPS		
LLS3 (Low Leakage Stop)	State retention power mode. LLWU, LPTMR, RTC, CMP, TSI can be operational. All of the radio Sea of Gates(SOG) logic is in state retention	Wakeup Interrupt	Radio SOG is in state retention in LLSx. The BLE/ 802.15.4/Generic FSK DSM ²
LLS2 (Low Leakage Stop)	State retention power mode. LLWU, LPTMR, RTC, CMP, TSI can be operational. 16 KB or 32 KB of programmable RAM can be powered on. All of the radio SOG logic is in state retention	Wakeup Interrupt	logic can be active using the 32 kHz clock
VLLS3 (Very Low Leakage Stop3)	Full SRAM retention. LLWU, LPTMR, RTC, CMP, TSI can be operational. All of the radio SOG logic is in state retention	Wakeup Reset	Radio SOG is in state retention in VLLS3/2. The BLE/802.15.4/Generic FSK
VLLS2 (Very Low Leakage Stop2)	Partial SRAM retention. 16 KB or 32 KB of programmable RAM can be powered on LLWU, LPTMR, RTC, CMP, TSI can be operational.All of the radio SOG logic is in state retention -	Wakeup Reset	DSM logic can be active using the 32 kHz clock
VLLS1 (Very Low Leakage Stop1) with RTC + 32 kHz OSC	All SRAM powered off. The 32-byte system register file remains powered for customer-critical data. LLWU, LPTMR, RTC, CMP can be operational. Radio logic is power gated.	Wakeup Reset	Radio operation not supported. The Radio SOG is power-gated in VLLS1/0. Radio state is lost at VLLS1
VLLS1 (Very Low Leakage Stop1) with LPTMR + LPO	All SRAM powered off. The 32-byte system register file remains powered for customer-critical data. LLWU, LPTMR, RTC, CMP, TSI can be operational.	Wakeup Reset	and lower power states
VLLS0 (Very Low Leakage Stop0) with Brown-out Detection	VLLS0 is not supported with DC-DC The 32-byte system register file remains powered for customer-critical data. Disable all analog modules in PMC and retains I/O state and DGO state. LPO disabled, POR brown-out detection enabled, Pin interrupt only. Radio logic is power gated.	Wakeup Reset	Radio operation not supported. The Radio digital is power-gated in VLLS1/0
VLLS0 (Very Low Leakage Stop0) without Brown-out	VLLS0 is not supported with DC-DC buck/boost configuration but is supported with bypass configuration	Wakeup Reset	
Detection	The 32-byte system register file remains powered for customer-critical data. Disable all analog modules in PMC and retains I/O state and DGO state. LPO disabled, POR brown-out detection disabled, Pin interrupt only. Radio logic is power gated.		

- 1. Biasing is disabled, but the Flash is in a low power mode for VLPx, so this configuration can realize some power savings over use of Run/Wait/Stop
- 2. DSM refers to Radio's deepsleep mode. DSM does not refer to the ARM sleep deep mode.

7 MCU Electrical Characteristics

7.1 AC electrical characteristics

Unless otherwise specified, propagation delays are measured from the 50% to the 50% point, and rise and fall times are measured at the 20% and 80% points, as shown in the following figure.

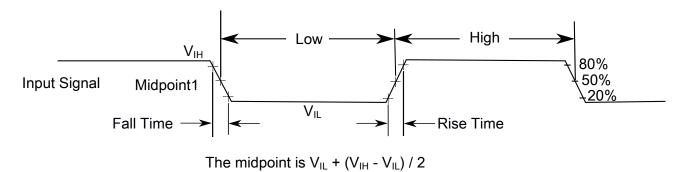


Figure 2. Input signal measurement reference

All digital I/O switching characteristics, unless otherwise specified, assume that the output pins have the following characteristics.

- $C_L = 30 \text{ pF loads}$
- Slew rate disabled
- Normal drive strength

7.2 Nonswitching electrical specifications

7.2.1 Voltage and current operating requirements

Table 10. Voltage and current operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
V_{DD}	Supply voltage	1.71	3.6	V	
V_{DDA}	Analog supply voltage	1.71	3.6	V	

Table 10. Voltage and current operating requirements (continued)

Symbol	Description	Min.	Max.	Unit	Notes
$V_{DD} - V_{DDA}$	V _{DD} -to-V _{DDA} differential voltage	-0.1	0.1	V	
V _{SS} – V _{SSA}	V _{SS} -to-V _{SSA} differential voltage	-0.1	0.1	V	
V _{IH}	Input high voltage				
	• 2.7 V ≤ V _{DD} ≤ 3.6 V	$0.7 \times V_{DD}$	_	V	
	• 1.7 V ≤ V _{DD} ≤ 2.7 V	$0.75 \times V_{DD}$	_	V	
V _{IL}	Input low voltage				
	• 2.7 V ≤ V _{DD} ≤ 3.6 V	_	$0.35 \times V_{DD}$	V	
	• 1.7 V ≤ V _{DD} ≤ 2.7 V	_	$0.3 \times V_{DD}$	V	
V _{HYS}	Input hysteresis	0.06 × V _{DD}	_	V	
licio	IO pin negative DC injection current — single pin $ \bullet \ \ V_{IN} < V_{SS} \text{-} 0.3 V $	-3	_	mA	1
I _{ICcont}	Contiguous pin DC injection current —regional limit, includes sum of negative injection currents of 16 contiguous pins				
	Negative current injection	-25	_	mA	
V _{ODPU}	Open drain pullup voltage level	V_{DD}	V_{DD}	V	2
V _{RAM}	V _{DD} voltage required to retain RAM	1.2	_	V	

All I/O pins are internally clamped to V_{SS} through a ESD protection diode. There is no diode connection to V_{DD}. If V_{IN} greater than V_{IO_MIN} (= V_{SS}-0.3 V) is observed, then there is no need to provide current limiting resistors at the pads. If this limit cannot be observed then a current limiting resistor is required. The negative DC injection current limiting resistor is calculated as R = (V_{IO_MIN} - V_{IN})/II_{ICIO}I.

7.2.2 LVD and POR operating requirements

Table 11. V_{DD} supply LVD and POR operating requirements

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
V _{POR}	Falling V _{DD} POR detect voltage	0.8	1.1	1.5	V	_
V _{LVDH}	Falling low-voltage detect threshold — high range (LVDV = 01)	2.48	2.56	2.64	V	
	Low-voltage warning thresholds — high range					1
V _{LVW1H}	• Level 1 falling (LVWV = 00)	2.62	2.70	2.78	V	
V_{LVW2H}	Level 2 falling (LVWV = 01)	2.72	2.80	2.88	V	
V _{LVW3H}	• Level 3 falling (LVWV = 10)	2.82	2.90	2.98	V	
V _{LVW4H}	Level 4 falling (LVWV = 11)	2.92	3.00	3.08	V	

^{2.} Open drain outputs must be pulled to V_{DD}.

Table 11. V_{DD} supply LVD and POR operating requirements (continued)

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
V _{HYSH}	Low-voltage inhibit reset/recover hysteresis — high range	_	±60	_	mV	_
V _{LVDL}	Falling low-voltage detect threshold — low range (LVDV=00)	1.54	1.60	1.66	V	_
	Low-voltage warning thresholds — low range					1
V _{LVW1L}	• Level 1 falling (LVWV = 00)	1.74	1.80	1.86	V	
V_{LVW2L}	 Level 2 falling (LVWV = 01) 	1.84	1.90	1.96	V	
V _{LVW3L}	• Level 3 falling (LVWV = 10)	1.94	2.00	2.06	V	
V _{LVW4L}	Level 4 falling (LVWV = 11)	2.04	2.10	2.16	V	
V _{HYSL}	Low-voltage inhibit reset/recover hysteresis — low range	_	±40	_	mV	_
V _{BG}	Bandgap voltage reference	0.97	1.00	1.03	V	_
t _{LPO}	Internal low power oscillator period — factory trimmed	900	1000	1100	μs	_

^{1.} Rising thresholds are falling threshold + hysteresis voltage

7.2.3 Voltage and current operating behaviors

Table 12. Voltage and current operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
V _{OH}	Output high voltage — Normal drive pad (except RESET_b) • $2.7 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V}, \text{I}_{OH} = -5 \text{ mA}$ • $1.71 \text{ V} \le \text{V}_{DD} \le 2.7 \text{ V}, \text{I}_{OH} = -2.5 \text{ mA}$	V _{DD} - 0.5 V _{DD} - 0.5	<u>-</u> -	V V	1, 2
V _{OH}	Output high voltage — High drive pad (except RESET_b) • $2.7 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V}$, $I_{OH} = -20 \text{ mA}$ • $1.71 \text{ V} \le \text{V}_{DD} \le 2.7 \text{ V}$, $I_{OH} = -10 \text{ mA}$	V _{DD} - 0.5 V _{DD} - 0.5	_ _	V V	1, 2
I _{OHT}	Output high current total for all ports	_	100	mA	
V _{OL}	Output low voltage — Normal drive pad $ \bullet \ \ 2.7 \ V \le V_{DD} \le 3.6 \ V, \ I_{OL} = 5 \ mA $ $ \bullet \ \ 1.71 \ V \le V_{DD} \le 2.7 \ V, \ I_{OL} = 2.5 \ mA $		0.5 0.5	V V	1
V _{OL}	Output low voltage — High drive pad $ \bullet \ \ 2.7 \ V \leq V_{DD} \leq 3.6 \ V, \ I_{OL} = 20 \ mA $ $ \bullet \ \ 1.71 \ V \leq V_{DD} \leq 2.7 \ V, \ I_{OL} = 10 \ mA $		0.5 0.5	V V	1
I _{OLT}	Output low current total for all ports	_	100	mA	

Table 12.	Voltage and current of	perating behaviors ((continued)

Symbol	Description	Min.	Max.	Unit	Notes
I _{IN}	Input leakage current (per pin) for full temperature range	_	500	nA	3
I _{IN}	Input leakage current (per pin) at 25 °C	_	0.025	μΑ	3
I _{IN}	Input leakage current (total all pins) for full temperature range	_	5	μА	3
R _{PU}	Internal pullup resistors	20	50	kΩ	4

^{1.} PTB0-1 and PTC0-3, PTC6, PTC7, PTC17, PTC18 I/O have both high drive and normal drive capability selected by the associated PTx_PCRn[DSE] control bit. All other GPIOs are normal drive only.

7.2.4 Power mode transition operating behaviors

All specifications except t_{POR} and VLLSx \rightarrow RUN recovery times in the following table assume this clock configuration:

- CPU and system clocks = 48 MHz
- Bus and flash clock = 24 MHz
- FEI clock mode

POR and VLLSx→RUN recovery use FEI clock mode at the default CPU and system frequency of 21 MHz, and a bus and flash clock frequency of 10.5 MHz.

Table 13. Power mode transition operating behaviors

Symbol	Description	Max.	Unit	Notes
t _{POR}	After a POR event, amount of time from the point V_{DD} reaches 1.8 V to execution of the first instruction across the operating temperature range of the chip.	300	μs	1
	• VLLS0 → RUN			
		147	μs	
	• VLLS1 → RUN			
		144	μs	
	VLLS2 → RUN			
		76	μs	
	• VLLS3 → RUN			
		76	μs	

^{2.} The reset pin only contains an active pull down device when configured as the RESET signal or as a GPIO. When configured as a GPIO output, it acts as a pseudo open drain output.

^{3.} Measured at V_{DD} = 3.6 V

^{4.} Measured at V_{DD} supply voltage = V_{DD} min and Vinput = V_{SS}

Table 13. Power mode transition operating behaviors (continued)

Symbol	Description	Max.	Unit	Notes
	• LLS2 → RUN	5.8	μs	
	• LLS3 → RUN			
		5.8	μs	
	• VLPS → RUN			
		6.2	μs	
	• STOP → RUN			
		6.2	μs	

^{1.} Normal boot (FTFA_FOPT[LPBOOT]=11). When the DC-DC converter is in bypass mode, TPOR will not meet the 300µs spec when 1) VDD_1P5 < 1.6V at 25°C and °C. 2) 1.5V ≤ VDD_1P5 ≤ 1.8V. For the bypass mode special case where VDD_1P5 = VDD_1P8, TPOR did not meet the 300µs maximum spec when the supply slew rate <=100V/s.

7.2.5 Power consumption operating behaviors

Table 14. Power consumption operating behaviors - Bypass Mode

Symbol	Description	Тур.	Max.	Unit	Notes
I _{DDA}	Analog supply current	_	See note	mA	1
I _{DD_RUNCO_} CM	Run mode current in compute operation - 48 MHz core / 24 MHz flash / bus disabled, LPTMR running using LPO clock at 1kHz, CoreMark benchmark code executing from flash at 3.0 V	7.79	8.64	mA	2
I _{DD_RUNCO}	Run mode current in compute operation - 48 MHz core / 24 MHz flash / bus clock disabled, code of while(1) loop executing from flash at 3.0 V	4.6	5.45	mA	3
I _{DD_RUN}	Run mode current - 48 MHz core / 24 MHz bus and flash, all peripheral clocks disabled, code of while(1) loop executing from flash at 3.0 V	5.6	6.45	mA	3
I _{DD_RUN}	Run mode current - 48 MHz core / 24 MHz bus and flash, all peripheral clocks enabled, code of while(1) loop executing from flash at 3.0 V				3, 4
	at 25 °C	6.9	7.2	mA	
	at 85 °C	7.2	8	mA	
	at 105 °C	7.7	8.5	mA	
I _{DD_WAIT}	Wait mode current - core disabled / 48 MHz system / 24 MHz bus / flash disabled (flash doze enabled), all peripheral clocks disabled at 3.0 V	4.2	5.05	mA	3
I _{DD_WAIT}	Wait mode current - core disabled / 24 MHz system / 24 MHz bus / flash disabled (flash doze enabled), all peripheral clocks disabled at 3.0 V	3.5	4.35	mA	3
I _{DD_PSTOP2}	Stop mode current with partial stop 2 clocking option - core and system disabled / 10.5 MHz bus at 3.0 V	2.7	3.55	mA	3

Table 14. Power consumption operating behaviors - Bypass Mode (continued)

Symbol	Description	Тур.	Max.	Unit	Notes
I _{DD_VLPRCO_} CM	Very-low-power run mode current in compute operation - 4 MHz core / 0.8 MHz flash / bus clock disabled, LPTMR running using LPO clock at 1 kHz reference clock, CoreMark benchmark code executing from flash at 3.0 V	760	960	μА	5
I _{DD_VLPRCO}	Very-low-power run mode current in compute operation - 4 MHz core / 0.8 MHz flash / bus clock disabled, code of while(1) loop executing from flash at 3.0 V	157	357	μА	6
I _{DD_VLPR}	Very-low-power run mode current - 4 MHz core / 0.8 MHz bus and flash, all peripheral clocks disabled, code of while(1) loop executing from flash at 3.0 V	195	395	μА	6
I _{DD_VLPR}	Very-low-power run mode current - 4 MHz core / 0.8 MHz bus and flash, all peripheral clocks enabled, code of while(1) loop executing from flash at 3.0 V	250	450	μА	4, 6
I _{DD_VLPW}	Very-low-power wait mode current - core disabled / 4 MHz system / 0.8 MHz bus / flash disabled (flash doze enabled), all peripheral clocks disabled at 3.0 V	142	342	μА	6
I _{DD_STOP}	Stop mode current at 3.0 V				
	at 25 °C	0.204	0.294	mA	
	at 70 °C	0.275	0.692	mA	
	at 105 °C	0.561	1.3	mA	
I _{DD_VLPS}	Very-low-power stop mode current at Bypass mode(3.0 V),				
	at 25 °C	4.3	18	μA	
	at 70 °C	17	42	μΑ	
	at 105 °C	157	328	μA	
I _{DD_LLS3}	Low-leakage stop mode 3 current at Bypass mode(3.0 V),				
	at 25 °C	2.7	5	μA	
	at 70 °C	9	16.5	μΑ	
	at 105 °C	69	128	μΑ	
I _{DD_LLS2}	Low-leakage stop mode 2 current at Bypass mode(3.0 V),				
	at 25 °C	2	3.13	μΑ	
	at 70 °C	3.2	10.5	μΑ	
	at 105 °C	39	65.5	μA	
I _{DD_VLLS3}	Very-low-leakage stop mode 3 current at Bypass mode(3.0 V),				
	at 25 °C	2.3	4	μA	
	at 70 °C	15	28.5	μA	

Table 14. Power consumption operating behaviors - Bypass Mode (continued)

Symbol	Description	Тур.	Max.	Unit	Notes
	at 105 °C	58	108	μΑ	
I _{DD_VLLS2}	Very-low-leakage stop mode 2 current at Bypass mode(3.0 V),				
	at 25 °C	1.5	2.21	μA	
	at 70 °C	6.3	11.8	μΑ	
	at 105 °C	27	42.6	μΑ	
I _{DD_VLLS1}	Very-low-leakage stop mode 1 current at Bypass mode(3.0 V),				
	at 25°C	0.56	1.3	μA	
	at 70°C	3	9.4	μA	
	at 105°C	16.8	27.1	μA	
I _{DD_VLLS0}	Very-low-leakage stop mode 0 current (SMC_STOPCTRL[PORPO] = 0) at 3.0 V				
	at 25 °C	0.36	0.949	μA	
	at 70 °C	2.7	8.2	μA	
	at 105 °C	16.5	27	μA	
I _{DD_VLLS0}	Very-low-leakage stop mode 0 current (SMC_STOPCTRL[PORPO] = 1) at 3.0 V				7
	at 25 °C	0.182	0.765	μA	
	at 70 °C	2.5	6.7	μA	
	at 105 °C	16.3	26	μA	

- 1. The analog supply current is the sum of the active or disabled current for each of the analog modules on the device. See each module's specification for its supply current.
- 2. MCG configured for FEImode. CoreMark benchmark compiled using IAR 7.70 with optimization level high, optimized for balanced.
- 3. MCG configured for FEI mode.
- 4. Incremental current consumption from peripheral activity is not included.
- 5. MCG configured for BLPI mode. CoreMark benchmark compiled using IAR 7.70 with optimization level high, optimized for balanced.
- 6. MCG configured for BLPI mode.
- 7. No brownout

Table 15. Power consumption operating behaviors - Buck Mode

Symbol	Description	Тур.	Max.	Unit	Notes
I _{DDA}	Analog supply current	_	See note	mA	1
I _{DD_RUNCO}	Run mode current in compute operation - 48 MHz core / 24 MHz flash / bus clock disabled, code of while(1) loop executing from flash at 3.0 V	3.1	_	mA	2
I _{DD_RUN}	Run mode current - 48 MHz core / 24 MHz bus and flash, all peripheral clocks disabled, code of while(1) loop executing from flash at 3.0 V	3.85	_	mA	2

Table 15. Power consumption operating behaviors - Buck Mode (continued)

Symbol	Description	Тур.	Max.	Unit	Notes
I _{DD_RUN}	Run mode current - 48 MHz core / 24 MHz bus and flash, all peripheral clocks enabled, code of while(1) loop executing from flash at 3.0 V				2, 3
	at 25 °C	4.8	_	mA	
	at 85 °C	5.3	_	mA	
	at 105 °C		_	mA	
Nait mode current - core disabled / 48 MHz system / 24 MHz bus / flash disabled (flash doze enabled), all peripheral clocks disabled at 3.0 V		3.1	_	mA	2
I _{DD_WAIT} Wait mode current - core disabled / 24 MHz system / 24 MHz bus / flash disabled (flash doze enabled), all peripheral clocks disabled at 3.0 V		2.9	_	mA	2
I _{DD_PSTOP2}	Stop mode current with partial stop 2 clocking option - core and system disabled / 10.5 MHz bus at 3.0 V	1.9	_	mA	2
Very-low-power run mode current in compute operation - 4 MHz core / 0.8 MHz flash / bus clock disabled, code of while(1) loop executing from flash at 3.0 V		137	_	μА	4
I _{DD_VLPR}	Very-low-power run mode current - 4 MHz core / 0.8 MHz bus and flash, all peripheral clocks disabled, code of while(1) loop executing from flash at 3.0 V	154	_	μА	-1
I _{DD_VLPR}	Very-low-power run mode current - 4 MHz core / 0.8 MHz bus and flash, all peripheral clocks enabled, code of while(1) loop executing from flash at 3.0 V	216	_	μА	3, 4
I _{DD_VLPW}	Very-low-power wait mode current - core disabled / 4 MHz system / 0.8 MHz bus / flash disabled (flash doze enabled), all peripheral clocks disabled at 3.0 V	131	_	μА	4
I _{DD_STOP}	Stop mode current at 3.0 V				
	at 25 °C	1.61	2.32	mA	
	at 70 °C	1.73	4.35	mA	
	at 105 °C	2.02	4.68	mA	
I _{DD_VLPS}	Very-low-power stop mode current at Buck mode(3.0 V),				
	at 25 °C	3.58	14.98	μΑ	
	at 70 °C	15.08	37.27	μΑ	
	at 105 °C	116.94	244.30	μΑ	
I _{DD_LLS3}	Low-leakage stop mode 3 current at Buck mode(3.0 V),				
	at 25 °C	2.20	4.08	μΑ	
	at 70 °C	7.44	13.63	μΑ	
	at 105 °C	48.78	90.49	μΑ	

Table 15. Power consumption operating behaviors - Buck Mode (continued)

Symbol	Description	Тур.	Max.	Unit	Notes
I _{DD_LLS2}	Low-leakage stop mode 2 current at Buck mode(3.0 V),				
	at 25 °C	1.86	2.91	μΑ	
	at 70 °C	3.19	10.48	μΑ	
	at 105 °C	31.44	52.80	μΑ	
I _{DD_VLLS3}	Very-low-leakage stop mode 3 current at Buck mode(3.0 V),				
	at 25 °C	1.79	3.12	μΑ	
	at 70 °C	12	22.8	μΑ	
	at 105 °C	37.49	69.81	μΑ	
I _{DD_VLLS2}	Very-low-leakage stop mode 2 current at Buck mode(3.0 V),				
	at 25 °C	1.09	1.60	μΑ	
	at 70 °C	5.56	10.40	μΑ	
	at 105 °C	18.71	29.52	μΑ	
I _{DD_VLLS1}	Very-low-leakage stop mode 1 current at Buck mode(3.0 V),				
	at 25 °C	0.46	1.07	μΑ	
	at 70 °C	2.17	6.8	μΑ	
	at 105 °C	14.08	22.71	μΑ	

^{1.} The analog supply current is the sum of the active or disabled current for each of the analog modules on the device. See each module's specification for its supply current.

Table 16. Power consumption operating behaviors - Boost Mode

Symbol	Description	Тур.	Max.	Unit	Notes
I _{DDA}	Analog supply current	_	See note	mA	1
I _{DD_RUNCO}	Run mode current in compute operation - 48 MHz core / 24 MHz flash / bus clock disabled, code of while(1) loop executing from flash at 1.3 V	8.1	_	mA	2
I _{DD_RUN}	Run mode current - 48 MHz core / 24 MHz bus and flash, all peripheral clocks disabled, code of while(1) loop executing from flash at 1.3 V	9.76	_	mA	2
I _{DD_RUN}	Run mode current - 48 MHz core / 24 MHz bus and flash, all peripheral clocks enabled, code of while(1) loop executing from flash at 1.3 V				2, 3
	at 25 °C	13.2	_	mA	
	at 85 °C	14.1	_	mA	

^{2.} MCG configured for FEI mode.

^{3.} Incremental current consumption from peripheral activity is not included.

^{4.} MCG configured for BLPI mode.

Table 16. Power consumption operating behaviors - Boost Mode (continued)

Symbol	Description	Тур.	Max.	Unit	Notes
	at 105 °C	15.2	_	mA	
I _{DD_WAIT}	Wait mode current - core disabled / 48 MHz system / 24 MHz bus / flash disabled (flash doze enabled), all peripheral clocks disabled at 1.3 V	6.9	_	mA	2
I _{DD_WAIT}	Wait mode current - core disabled / 24 MHz system / 24 MHz bus / flash disabled (flash doze enabled), all peripheral clocks disabled at 1.3 V	5.8	_	mA	2
I _{DD_PSTOP2}	Stop mode current with partial stop 2 clocking option - core and system disabled / 10.5 MHz bus at 1.3 V	8.3	_	mA	2
I _{DD_VLPRCO}	Very-low-power run mode current in compute operation - 4 MHz core / 0.8 MHz flash / bus clock disabled, code of while(1) loop executing from flash at 1.3 V	378	_	μА	4
I _{DD_VLPR}	Very-low-power run mode current - 4 MHz core / 0.8 MHz bus and flash, all peripheral clocks disabled, code of while(1) loop executing from flash at 1.3 V	476	_	μА	4
I _{DD_VLPR}			_	μА	3, 4
I _{DD_VLPW}	Very-low-power wait mode current - core disabled / 4 MHz system / 0.8 MHz bus / flash disabled (flash doze enabled), all peripheral clocks disabled at 1.3 V	357	_	μА	4
I _{DD_STOP}	Stop mode current at 1.3 V	3.22	4.64	mA	
	at 25 °C	3.56	8.96	mA	
	at 70 °C	3.74	9.73	mA	
	at 105 °C	0.74	3.70	IIIA	
I _{DD_VLPS}	Very-low-power stop mode current at Boost mode(1.3 V),				
	at 25 °C	29.89	125.13	μA	
	at 70 °C	191.62	473.41	μA	
	at 105 °C	1429.24	2985.93	μA	
I _{DD_LLS3}	Low-leakage stop mode 3 current at Boost mode(1.3 V),				
	at 25 °C	12.16	22.53	μA	
	at 70 °C	84.61	155.12	μΑ	
	at 105 °C	534.09	990.79	μA	
I _{DD_LLS2}	Low-leakage stop mode 2 current at Boost mode(1.3 V),				
	at 25 °C	12.05	18.86	μA	
	at 70 °C	17.36	56.96	μA	
	at 105 °C	221.29	371.66	μA	

Table 16. Power consumption operating behaviors - Boost Mode (continued)

Symbol	Description	Тур.	Max.	Unit	Notes
I _{DD_VLLS3}	Very-low-leakage stop mode 3 current at Boost mode(1.3 V),				
	at 50 °C	7.99	13.89	μΑ	
	at 70 °C	88.4	167.96	μΑ	
	at 85 °C	287.14	534.67	μΑ	
I _{DD_VLLS2}	Very-low-leakage stop mode 2 current at Boost mode(1.3 V),				
	at 25 °C	7.09	10.45	μΑ	
	at 70 °C	23.38	43.79	μΑ	
	at 85 °C	95.67	150.94	μΑ	
I _{DD_VLLS1}	Very-low-leakage stop mode 1 current at Boost mode(1.3 V),				
	at 25 °C	3.63	8.44	μΑ	
	at 70 °C	16.23	50.86	μΑ	
	at 105 °C	67.77	109.32	μΑ	

^{1.} The analog supply current is the sum of the active or disabled current for each of the analog modules on the device. See each module's specification for its supply current.

Table 17. Low power mode peripheral adders — typical value

Symbol	Description		Tem	perature	e (°C)		Unit
		-40	25	50	70	85	
I _{IREFSTEN4MHz}	I _{IREFSTEN4MHz} 4 MHz internal reference clock (IRC) adder. Measured by entering STOP or VLPS mode with 4 MHz IRC enabled.		46	47	47	47	μA
lirefsten32kHz	32 kHz internal reference clock (IRC) adder. Measured by entering STOP mode with the 32 kHz IRC enabled.	88	91	90	89	88	μA
lerefsten32kHz	External 32 kHz crystal clock adder by means of the RTC bits. Measured by entering all modes with the crystal enabled.						
	VLLS1	1.4	1.3	1.6	2.4	4.1	
	VLLS2	1.6	1.5	1.9	4.2	7.7	μΑ
	VLLS3	2.7	1.9	2.9	7.7	15	
	LLS2	1.8	1.4	1.7	4.1	8	
	LLS3	2.6	1.7	2.8	7.6	15.2	
I _{CMP}	CMP peripheral adder measured by placing the device in VLLS1 mode with	22	19	20	21	21	μA

^{2.} MCG configured for FEI mode.

^{3.} Incremental current consumption from peripheral activity is not included.

^{4.} MCG configured for BLPI mode.

Table 17. Low power mode peripheral adders — typical value (continued)

Symbol	Description		Tem	perature	e (°C)		Unit
		-40	25	50	70	85	
	CMP enabled using the 6-bit DAC and a single external input for compare. Includes 6-bit DAC power consumption.						
Івтс	I _{RTC} RTC peripheral adder measured by placing the device in VLLS1 mode with external 32 kHz crystal enabled by means of the RTC_CR[OSCE] bit and the RTC ALARM set for 1 minute. Includes ERCLK32K (32 kHz external crystal) power consumption.		1.3	1.6	2.4	4.3	μА
I _{LPUART}	LPUART peripheral adder measured by placing the device in STOP or VLPS mode with selected clock source waiting for RX data at 115200 baud rate. Includes selected clock source power consumption.						
	MCGIRCLK (4 MHz internal reference clock)	53	54	54	54	54	μΑ
I _{LPTMR}	LPTMR peripheral adder measured by placing the device in VLLS1 mode with LPTMR enabled using LPO.						
		30	30	30	85	100	nA
I _{TPM}	TPM peripheral adder measured by placing the device in STOP or VLPS mode with selected clock source configured for output compare generating 100 Hz clock signal. No load is placed on the I/O generating the clock signal. Includes selected clock source and I/O switching currents. MCGIRCLK (4 MHz internal reference	58	59	59	59	59	μА
	clock)						
I _{BG}	Bandgap adder when BGEN bit is set and device is placed in VLPx, LLS, or VLLSx mode.	76	82	85	87	87	μА
I _{ADC}	I _{ADC} ADC peripheral adder combining the measured values at V _{DD} and V _{DDA} by placing the device in STOP or VLPS mode. ADC is configured for low-power mode using the internal clock and continuous conversions.		327	327	327	328	μА

7.2.6 Diagram: Typical IDD_RUN operating behavior

The following data was measured from previous devices with same MCU core (ARM® Cortex-M0+) under these conditions:

- No GPIOs toggled
- Code execution from flash with cache enabled
- For the ALLOFF curve, all peripheral clocks are disabled except FTFA

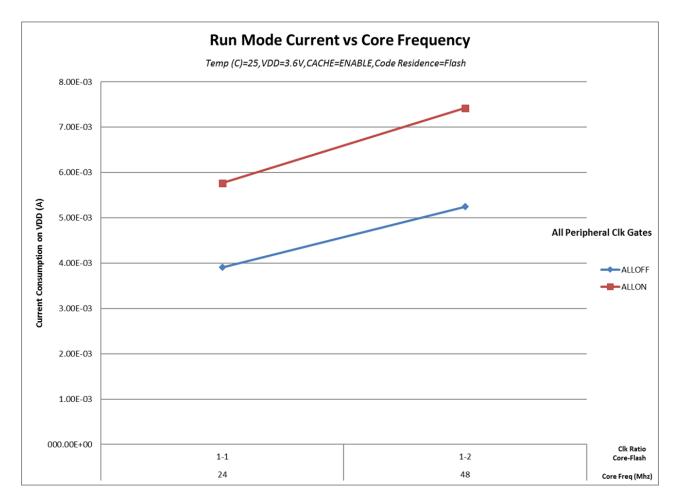


Figure 3. Run mode supply current vs. core frequency

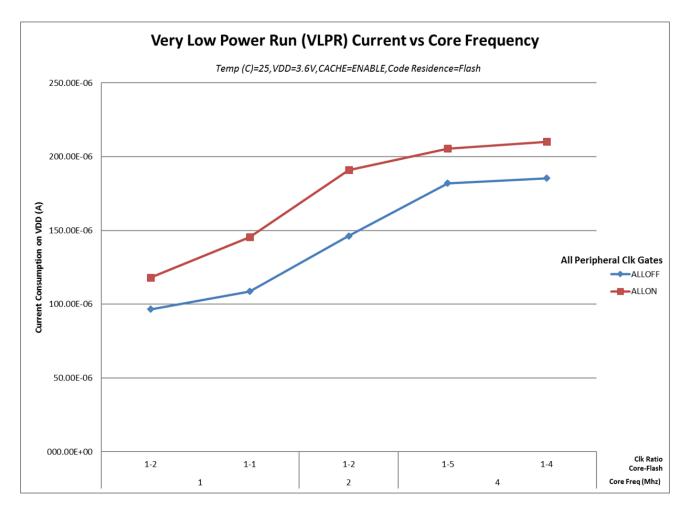


Figure 4. VLPR mode current vs. core frequency

7.2.7 SoC Power Consumption

Full KW41Z/31Z/21Z system-on-chip (SoC) power consumption is a function of the many configurations possible for the MCU platform and its peripherals including the 2.4GHz radio and the DC-DC converter. A few measured SoC configurations are as follows:

MCU State Flash State **Radio State DCDC State** Typical Unit Average IC current Buck(VDD_{DCDC in}=3.6 V) **STOP** Doze Rx 8.4 mΑ Buck(VDD_{DCDC in}=3.6 V) **STOP** Doze Tx(at 0 dBm) 7.6 mΑ RUN Enabled RxBuck(VDD_{DCDC in}=3.6 V) 10.2 mΑ

Table 18. SoC Power Consumption

Table 18. SoC Power Consumption (continued)

MCU State	Flash State	Radio State	DCDC State	Typical Average IC current	Unit
RUN	Enabled	Tx(at 0 dBm)	Buck(VDD _{DCDC_in} =3.6 V)	9.6	mA
STOP	Doze	Rx	Disabled/Bypass	16.6	mA
STOP	Doze	Tx(at 0 dBm)	Disabled/Bypass	15.2	mA
RUN	Enabled	Rx	Disabled/Bypass	19.7	mA
RUN	Enabled	Tx(at 0 dBm)	Disabled/Bypass	19.2	mA

7.2.8 Designing with radiated emissions in mind

To find application notes that provide guidance on designing your system to minimize interference from radiated emissions:

- 1. Go to www.nxp.com
- 2. Perform a keyword search for "EMC design."

7.2.9 Capacitance attributes

Table 19. Capacitance attributes

Symbol	Description	Min.	Max.	Unit
C _{IN}	Input capacitance	_	7	pF

7.3 Switching electrical specifications

7.3.1 Device clock specifications

Table 20. Device clock specifications

Symbol	Description	Min.	Max.	Unit
	Normal run mode			
f _{SYS}	System and core clock	_	48	MHz
f _{BUS}	Bus clock	_	24	MHz
f _{FLASH}	Flash clock	_	24	MHz

Table 20. D	evice clock s	pecifications ((continued)	,
-------------	---------------	-----------------	-------------	---

Symbol	Description	Min.	Max.	Unit
f _{LPTMR}	LPTMR clock	_	24	MHz
	VLPR and VLPS modes ¹			
f _{SYS}	System and core clock	_	4	MHz
f _{BUS}	Bus clock	_	1	MHz
f _{FLASH}	Flash clock	_	1	MHz
f _{LPTMR}	LPTMR clock ²	_	24	MHz
f _{ERCLK}	External reference clock	_	16	MHz
f _{LPTMR_ERCLK}	LPTMR external reference clock	_	16	MHz
f _{TPM}	TPM asynchronous clock	_	8	MHz
f _{LPUART0}	LPUART0 asynchronous clock	_	12	MHz

^{1.} The frequency limitations in VLPR and VLPS modes here override any frequency specification listed in the timing specification for any other module. These same frequency limits apply to VLPS, whether VLPS was entered from RUN or from VLPR.

7.3.2 General switching specifications

These general-purpose specifications apply to all signals configured for GPIO, LPUART, CMT and I^2C signals.

Table 21. General switching specifications

Description	Min.	Max.	Unit	Notes
GPIO pin interrupt pulse width (digital glitch filter disabled) — Synchronous path	1.5	-	Bus clock cycles	1, 2
NMI_b pin interrupt pulse width (analog filter enabled) — Asynchronous path	200	-	ns	3
GPIO pin interrupt pulse width (digital glitch filter disabled, analog filter disabled) — Asynchronous path	20	-	ns	3
External RESET_b input pulse width (digital glitch filter disabled)	100	-	ns	
Port rise and fall time(low drive strength)				4, 5
Slew enabled	-	25	ns	
 1.71 ≤ VDD ≤ 2.7 V 2.7 ≤ VDD ≤ 3.6 V 	-	16	ns	
Slew disabled	-	8	ns	
 1.71 ≤ VDD ≤ 2.7 V 2.7 ≤ VDD ≤ 3.6 V 	-	6	ns	
Port rise and fall time(low drive strength)	-	24	ns	6, 7
Slew enabled	-	16	ns	

^{2.} The LPTMR can be clocked at this speed in VLPR or VLPS only when the source is an external pin.

Table 21. General switching specifications

Description	Min.	Max.	Unit	Notes
• 1.71 ≤ VDD ≤ 2.7 V	-	10	ns	
 2.7 ≤ VDD ≤ 3.6 V Slew disabled 	-	6	ns	
 1.71 ≤ VDD ≤ 2.7 V 2.7 ≤ VDD ≤ 3.6 V 				

- 1. This is the minimum pulse width that is guaranteed to pass through the pin synchronization circuitry in run modes.
- 2. The greater of synchronous and asynchronous timing must be met.
- 3. This is the minimum pulse width that is guaranteed to be recognized
- 4. PTB0, PTB1, PTC0, PTC1, PTC2, PTC3, PTC6, PTC7, PTC17, PTC18.
- 5. 75 pF load.
- 6. Ports A, B, and C.
- 7. 25 pF load.

7.4 Thermal specifications

7.4.1 Thermal operating requirements

Table 22. Thermal operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
T _J	Die junction temperature	-40	125	°C	
	For Laminate QFN package				
T _A	Ambient temperature	-40	105	°C	1
	For Laminate QFN package				

^{1.} Maximum T_A can be exceeded only if the user ensures that T_J does not exceed the maximum. The simplest method to determine T_J is: $T_J = T_A + R_{\theta JA} \times$ chip power dissipation.

7.4.2 Thermal attributes

Table 23. Thermal attributes

Board type	Symbol	Description	48-pin Laminate QFN	Unit	Notes
Single-layer (1S)	$R_{\theta JA}$	Thermal resistance, junction to ambient (natural convection)	59.3	°C/W	1
Four-layer (2s2p)	$R_{ hetaJA}$	Thermal resistance, junction to ambient (natural convection)	42.9	°C/W	
Single-layer (1S)	$R_{ hetaJMA}$	Thermal resistance, junction to ambient (200 ft./min. air speed)	51.6	°C/W	

Table 23.	Thermal	attributes	(continued)

Board type	Symbol	Description	48-pin Laminate QFN	Unit	Notes
Four-layer (2s2p)	$R_{\theta JMA}$	Thermal resistance, junction to ambient (200 ft./min. air speed)	38.9	°C/W	
_	R _{0JB}	Thermal resistance, junction to board	37.7	°C/W	2
_	R _{eJC}	Thermal resistance, junction to case	0.48	°C/W	3
_	$\Psi_{ m JT}$	Thermal characterization parameter, junction to package top outside center (natural convection)	0.2	°C/W	4

- 1. Determined according to JEDEC Standard JESD51-2, Integrated Circuits Thermal Test Method Environmental Conditions—Natural Convection (Still Air), or EIA/JEDEC Standard JESD51-6, Integrated Circuit Thermal Test Method Environmental Conditions—Forced Convection (Moving Air).
- 2. Determined according to JEDEC Standard JESD51-8, *Integrated Circuit Thermal Test Method Environmental Conditions—Junction-to-Board*.
- 3. Determined according to Method 1012.1 of MIL-STD 883, *Test Method Standard, Microcircuits*, with the cold plate temperature used for the case temperature. The value includes the thermal resistance of the interface material between the top of the package and the cold plate.
- 4. Determined according to JEDEC Standard JESD51-2, Integrated Circuits Thermal Test Method Environmental Conditions—Natural Convection (Still Air).

7.5 Peripheral operating requirements and behaviors

7.5.1 Core modules

7.5.1.1 SWD electricals

Table 24. SWD full voltage range electricals

Symbol	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
J1	SWD_CLK frequency of operation			
	Serial wire debug	0	25	MHz
J2	SWD_CLK cycle period	1/J1	_	ns
J3	SWD_CLK clock pulse width			
	Serial wire debug	20	_	ns
J4	SWD_CLK rise and fall times	_	3	ns
J9	SWD_DIO input data setup time to SWD_CLK rise	10	_	ns
J10	SWD_DIO input data hold time after SWD_CLK rise	0	_	ns
J11	SWD_CLK high to SWD_DIO data valid	_	32	ns
J12	SWD_CLK high to SWD_DIO high-Z	5	_	ns

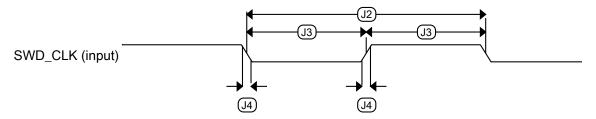


Figure 5. Serial wire clock input timing

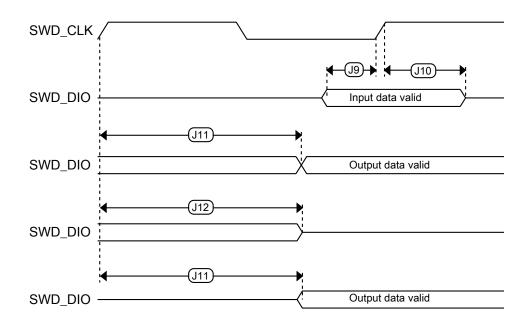


Figure 6. Serial wire data timing

7.5.2 System modules

There are no specifications necessary for the device's system modules.

7.5.3 Clock modules

7.5.3.1 MCG specifications

Table 25. MCG specifications

Symbol	Description		Min.	Тур.	Max.	Unit	Notes
f _{ints_ft}		frequency (slow clock) — nominal V _{DD} and 25 °C	_	32.768	_	kHz	
f _{ints_t}	Internal reference user trimmed	frequency (slow clock) —	31.25	_	39.0625	kHz	
$\Delta_{fdco_res_t}$	frequency at fixed	med average DCO output voltage and temperature — I] and C4[SCFTRIM]	_	± 0.3	± 0.6	%f _{dco}	1
Δf_{dco_t}		trimmed average DCO output Itage and temperature	_	+0.5/-0.7	± 3	%f _{dco}	1, 2
Δf _{dco_t}		trimmed average DCO output ed voltage and temperature	_	± 0.4	± 1.5	%f _{dco}	1, 2
f _{intf_ft}		frequency (fast clock) — nominal V _{DD} and 25 °C	_	4	_	MHz	
Δf _{intf_ft}	(fast clock) over te	on of internal reference clock emperature and voltage — nominal V _{DD} and 25 °C	_	+1/-2	± 3	% f _{intf_ft}	2
f _{intf_t}	Internal reference trimmed at nomina	frequency (fast clock) — user al V _{DD} and 25 °C	3	_	5	MHz	
f _{loc_low}	Loss of external c	lock minimum frequency —	(3/5) x f _{ints_t}	_	_	kHz	
f _{loc_high}	Loss of external c RANGE = 01, 10,	lock minimum frequency — or 11	(16/5) x f _{ints_t}	_	_	kHz	
FLL				•			
f _{fll_ref}	FLL reference free	quency range	31.25	_	39.0625	kHz	
f _{dco}	DCO output frequency range	Low range (DRS = 00) 640 × f _{fil_ref}	20	20.97	25	MHz	3, 4
		Mid range (DRS = 01) 1280 × f _{fll ref}	40	41.94	48	MHz	
f _{dco_t_DMX3}	DCO output frequency	Low range (DRS = 00) $732 \times f_{\text{fll_ref}}$	_	23.99	_	MHz	5, 6
		Mid range (DRS = 01)	_	47.97	_	MHz	
		1464 × f _{fll_ref}					
J _{cyc_fll}	FLL period jitter		_	180	_	ps	7
	• f _{VCO} = 48 M	Hz					
t _{fll_acquire}	FLL target frequer	ncy acquisition time		_	1	ms	8

^{1.} This parameter is measured with the internal reference (slow clock) being used as a reference to the FLL (FEI clock mode).

^{2.} The deviation is relative to the factory trimmed frequency at nominal V_{DD} and 25 °C, f_{ints_ft}.

^{3.} These typical values listed are with the slow internal reference clock (FEI) using factory trim and DMX32 = 0.

^{4.} The resulting system clock frequencies must not exceed their maximum specified values. The DCO frequency deviation (Δf_{dco_t}) over voltage and temperature must be considered.

- 5. These typical values listed are with the slow internal reference clock (FEI) using factory trim and DMX32 = 1.
- 6. The resulting clock frequency must not exceed the maximum specified clock frequency of the device.
- 7. This specification is based on standard deviation (RMS) of period or frequency.
- 8. This specification applies to any time the FLL reference source or reference divider is changed, trim value is changed, DMX32 bit is changed, DRS bits are changed, or changing from FLL disabled (BLPE, BLPI) to FLL enabled (FEI, FEE, FBE, FBI). If a crystal/resonator is being used as the reference, this specification assumes it is already running.

7.5.3.2 Reference Oscillator Specification

The KW41Z SoC has been designed to meet targeted specifications with a +/-20ppm frequency error over the life of the part, which includes the temperature, mechanical and aging excursions.

The table below shows typical specifications for the Crystal Oscillator to be used with KW41Z.

Table 26. Reference Crystal Specification

Symbol	Description	Comment 32M 26M			Unit				
		·	Min	Тур	Max	Min	Тур	Max	
	Operating Temperature		-40		105	-40		105	°C
Faging	Frequency accuracy over aging	1st year	-5		5	-5		5	ppm - 1st yr
iFacc	Initial Frequency accuracy	with respect to XO	-10		10	-10		10	ppm
Fstab	Frequency stability	across temperature, mechanical, load and voltage changes	-10		10	-10		10	ppm
CL	Values of CL supported(Integr ated on die and programmable)		7	10	13	7	10	13	pF
Co	Shunt parasitic capacitance		0.469	0.67	0.871	0.42	0.6	0.78	pF
Cm1	Motional capacitance Cm1		1.435	2.05	2.665	1.435	2.05	2.665	fF
Lm1	Motional inductance Lm1		8.47	12.1	15.73	12.81	18.3	23.79	mH
TS	Trim Sensitivity (TS) for the supported [Co,CL] values		6.30	9.00	11.70	6.39	9.12	11.86	ppm/pF

Symbol	Description	Comment	32M		26M			Unit	
			Min	Тур	Max	Min	Тур	Max	
Rm1	ESR: Maximum value of Rm1			25	60		35	60	Ohms
	Maximum crystal drive level limit				200			200	μW

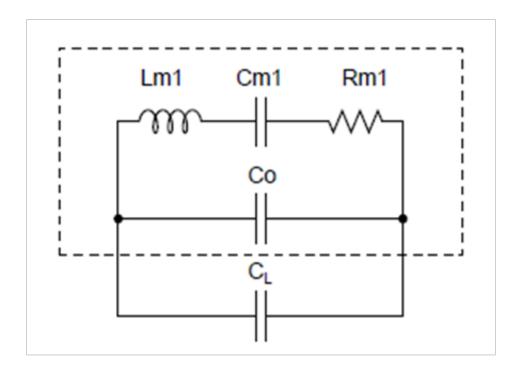


Figure 7. Crystal Electrical Block Diagram

7.5.4 Memories and memory interfaces

7.5.4.1 Flash electrical specifications

This section describes the electrical characteristics of the flash memory module.

7.5.4.1.1 Flash timing specifications — program and erase

The following specifications represent the amount of time the internal charge pumps are active and do not include command overhead.

Table 27. NVM program/erase timing specifications

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
t _{hvpgm4}	Longword Program high-voltage time	_	7.5	18	μs	_
t _{hversscr}	Sector Erase high-voltage time	_	13	113	ms	1
t _{hversblk256k}	Erase Block high-voltage time for 256 KB	_	104	904	ms	1

1. Maximum time based on expectations at cycling end-of-life.

7.5.4.1.2 Flash timing specifications — commands Table 28. Flash command timing specifications

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
	Read 1s Block execution time					1
t _{rd1blk256k}	256 KB program flash	_	_	1.7	ms	
t _{rd1sec2k}	Read 1s Section execution time (flash sector)	_	_	60	μs	1
t _{pgmchk}	Program Check execution time	_	_	45	μs	1
t _{rdrsrc}	Read Resource execution time	_	_	30	μs	1
t _{pgm4}	Program Longword execution time	_	65	145	μs	_
	Erase Flash Block execution time					2
t _{ersblk256k}	256 KB program flash	_	250	1500	ms	
t _{ersscr}	Erase Flash Sector execution time	_	14	114	ms	2
t _{rd1all}	Read 1s All Blocks execution time	_	_	1.8	ms	1
t _{rdonce}	Read Once execution time	_	_	30	μs	1
t _{pgmonce}	Program Once execution time	_	100	_	μs	_
t _{ersall}	Erase All Blocks execution time	_	500	3000	ms	2
t _{vfykey}	Verify Backdoor Access Key execution time	_	_	30	μs	1
t _{ersallu}	Erase All Blocks Unsecure execution time	_	500	3000	ms	2

^{1.} Assumes 25 MHz flash clock frequency.

7.5.4.1.3 Flash high voltage current behaviors Table 29. Flash high voltage current behaviors

Symbol	Description	Min.	Тур.	Max.	Unit
I _{DD_PGM}	Average current adder during high voltage flash programming operation	_	2.5	6.0	mA
I _{DD_ERS}	Average current adder during high voltage flash erase operation	_	1.5	4.0	mA

^{2.} Maximum times for erase parameters based on expectations at cycling end-of-life.

7.5.4.1.4 Reliability specifications Table 30. NVM reliability specifications

Symbol	Description	Min.	Typ. ¹	Max.	Unit	Notes			
	Program Flash								
t _{nvmretp10k}	Data retention after up to 10 K cycles	5	50	_	years	_			
t _{nvmretp1k}	Data retention after up to 1 K cycles	20	100	_	years	_			
n _{nvmcycp}	Cycling endurance	10 K	50 K	_	cycles	2			

Typical data retention values are based on measured response accelerated at high temperature and derated to a constant 25 °C use profile. Engineering Bulletin EB618 does not apply to this technology. Typical endurance defined in Engineering Bulletin EB619.

7.5.5 Security and integrity modules

There are no specifications necessary for the device's security and integrity modules.

7.5.6 Analog

7.5.6.1 ADC electrical specifications

All other ADC channels meet the 13-bit differential/12-bit single-ended accuracy specifications. The following specification is defined with the DC-DC converter operating in Bypass mode.

7.5.6.1.1 16-bit ADC operating conditions Table 31. 16-bit ADC operating conditions

Symbol	Description	Conditions	Min.	Typ. ¹	Max.	Unit	Notes
V_{DDA}	Supply voltage	Absolute	1.71	_	3.6	V	
ΔV_{DDA}	Supply voltage	Delta to V _{DD} (V _{DD} – V _{DDA})	-100	0	+100	mV	2
ΔV _{SSA}	Ground voltage	Delta to V _{SS} (V _{SS} – V _{SSA})	-100	0	+100	mV	2
V _{REFH}	ADC reference voltage high		1.13	V_{DDA}	V_{DDA}	V	3
V _{REFL}	ADC reference voltage low		V _{SSA}	V _{SSA}	V _{SSA}	V	3
V _{ADIN}	Input voltage	16-bit differential mode	VSSA	_	31/32 × VREFH	V	
		All other modes	VSSA	_	VREFH		

^{2.} Cycling endurance represents number of program/erase cycles at −40 °C ≤ T_i ≤ 125 °C.

Table 31. 16-bit ADC operating conditions (continued)

Symbol	Description	Conditions	Min.	Typ. ¹	Max.	Unit	Notes
C _{ADIN}	Input	16-bit mode	_	8	10	pF	
	capacitance	8-bit / 10-bit / 12-bit modes	_	4	5		
R _{ADIN}	Input series resistance		_	2	5	kΩ	
R _{AS}	Analog source	13-bit / 12-bit modes					4
	resistance (external)	f _{ADCK} < 4 MHz	_	_	5	kΩ	
f _{ADCK}	ADC conversion clock frequency	≤ 13-bit mode	1.0	_	18.0	MHz	5
f _{ADCK}	ADC conversion clock frequency	16-bit mode	2.0	_	12.0	MHz	5
C _{rate}	ADC conversion	≤ 13-bit modes					6
	rate	No ADC hardware averaging	20.000	_	818.330	ksps	
		Continuous conversions enabled, subsequent conversion time					
C _{rate}	ADC conversion	16-bit mode					6
	rate	No ADC hardware averaging	37.037	_	461.467	ksps	
		Continuous conversions enabled, subsequent conversion time					

- 1. Typical values assume $V_{DDA} = 3.0 \text{ V}$, Temp = 25 °C, $f_{ADCK} = 1.0 \text{ MHz}$, unless otherwise stated. Typical values are for reference only, and are not tested in production.
- 2. DC potential difference.
- 3. For packages without dedicated VREFH and VREFL pins, V_{REFH} is internally tied to V_{DDA} , and V_{REFL} is internally tied to V_{SSA} .
- 4. This resistance is external to MCU. To achieve the best results, the analog source resistance must be kept as low as possible. The results in this data sheet were derived from a system that had < 8 Ω analog source resistance. The R_{AS}/C_{AS} time constant should be kept to < 1 ns.
- 5. To use the maximum ADC conversion clock frequency, CFG2[ADHSC] must be set and CFG1[ADLPC] must be clear.
- 6. For guidelines and examples of conversion rate calculation, download the ADC calculator tool.

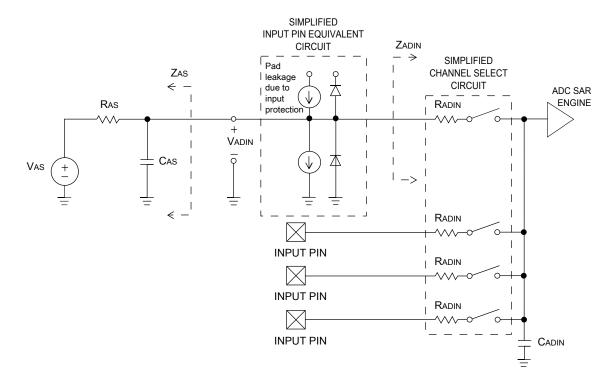


Figure 8. ADC input impedance equivalency diagram

7.5.6.1.2 16-bit ADC electrical characteristics

Table 32. 16-bit ADC characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$)

Symbol	Description	Conditions ¹	Min.	Typ. ²	Max.	Unit	Notes		
I _{DDA_ADC}	Supply current		0.215	_	1.7	mA	3		
	ADC asynchronous	ADLPC=1, ADHSC=0	1.2	2.4	3.9	MHz	t _{ADACK} =		
	clock source	ADLPC=1, ADHSC=1	2.4	4.0	6.1	MHz	1/f _{ADACK}		
f _{ADACK}		ADLPC=0, ADHSC=0	3.0	5.2	7.3	MHz			
		ADLPC=0, ADHSC=1	4.4	6.2	9.5	MHz			
	Sample Time	See Reference Manual chapter	See Reference Manual chapter for sample times						
TUE	Total unadjusted	12-bit modes	_	±4	±6.8	LSB ⁴	5		
	error	• <12-bit modes	_	±1.4	±2.1				
DNL	Differential non-	12-bit mode; Buck	_	±0.7	-1.1 to +1.9	LSB ⁴	5		
	linearity	Mode ⁶ • 12-bit mode; Boost	_	±0.5	-1.1 to +1.9				
		Mode ⁶ • 12-bit mode; Bypass	_	±0.5	-1.1 to +1.9				
		Mode Mode							

Table 32. 16-bit ADC characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$) (continued)

Symbol	Description	Conditions ¹	Min.	Typ. ²	Max.	Unit	Notes
INL	Integral non- linearity	12-bit mode; Buck Mode ⁶	_	±1.0	-2.7 to +1.9	LSB ⁴	5
		12-bit mode; Boost Mode ⁶	_	±0.7	-2.7 to +1.9		
		12-bit mode; Bypass Mode	_	±0.6	-2.7 to +1.9		
E _{FS}	Full-scale error	12-bit modes	_	-4	-5.4	LSB ⁴	V _{ADIN} =
		• <12-bit modes	_	-1.4	-1.8		V_{DDA}^{5}
EQ	Quantization error	16-bit modes	_	-1 to 0	_	LSB ⁴	
		• ≤13-bit modes	_	_	±0.5		
ENOB	Effective number of bits	16-bit differential mode; Buck Mode ⁶					7
		• Avg = 32	12	12.75	_	bits	
		• Avg = 4	11.25	11.75	_	bits	
		16-bit single-ended mode; Buck Mode ⁶					
		• Avg = 32	11	11.5	_	bits	
		• Avg = 4	9.5	10.5	_	bits	
		16-bit differential mode; Boost Mode ⁶					
		• Avg = 32	11.5	12	_	bits	
		• Avg = 4	9.75	11	_	bits	
		16-bit single-ended mode; Boost Mode ⁶					
		• Avg = 32	11	11.5	_	bits	
		• Avg = 4	9.75	10.5	_	bits	
		16-bit differential mode; Bypass Mode					
		• Avg = 32	12.5	13	_	bits	
		• Avg = 4	11.25	12	_	bits	
		16-bit single-ended mode; Bypass Mode					
		• Avg = 32	11	11.75	_	bits	
		• Avg = 4	10	10.5	_	bits	
SINAD	Signal-to-noise plus distortion	See ENOB	(6.02 × EN	OB + 1.76	dB	
THD	Total harmonic distortion	16-bit differential mode; Buck Mode ⁶					-1
		• Avg = 32	_	-90	_	dB	

Table 32. 16-bit ADC characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$) (continued)

Symbol	Description	Conditions ¹	Min.	Typ. ²	Max.	Unit	Notes
		16-bit single-ended mode; Buck Mode ⁶	_	-88	_	dB	
		• Avg = 32					
		16-bit differential mode; Boost Mode ⁶	_	-89	_	dB	
		• Avg = 32					
		16-bit single-ended mode; Boost Mode ⁶	_	-89	_	dB	
		• Avg = 32					
		16-bit differential mode; Bypass Mode	_	-89	_	dB	
		• Avg = 32					
		16-bit single-ended mode; Bypass Mode	_	-87	_	dB	
		• Avg = 32					
SINAD	Signal-to-noise plus distortion	See ENOB	6	6.02 × EN	OB + 1.76	dB	
SFDR	Spurious free dynamic range	16-bit differential mode; Buck Mode ⁶					-1
	distortion	• Avg = 32	85	89	_	dB	
		16-bit single-ended mode; Buck Mode ⁶					
		• Avg = 32	85	87	_	dB	
		16-bit differential mode; Boost Mode ⁶					
		• Avg = 32	78	86	_	dB	
		16-bit single-ended mode; Boost Mode ⁶					
		• Avg = 32	85	87	_	dB	
		16-bit differential mode; Bypass Mode					
		• Avg = 32	87	94	_	dB	
		16-bit single-ended mode; Bypass Mode					
		• Avg = 32	85	88	_	dB	
E _{IL}	Input leakage error			I _{In} ×	R _{AS}	mV	I _{In} = leakage current

Table 32. 16-bit ADC characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$) (continued)

Symbol	Description	Conditions ¹	Min.	Typ. ²	Max.	Unit	Notes
							(refer to the MCU's voltage and current operating ratings)
	Temp sensor slope	Across the full temperature range of the device	1.55	1.62	1.69	mV/° C	8
V _{TEMP25}	Temp sensor voltage	25 °C	706	716	726	mV	8

- 1. All accuracy numbers assume the ADC is calibrated with $V_{REFH} = V_{DDA}$
- 2. Typical values assume V_{DDA} = 3.0 V, Temp = 25 °C, f_{ADCK} = 2.0 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.
- The ADC supply current depends on the ADC conversion clock speed, conversion rate and ADC_CFG1[ADLPC] (low power). For lowest power operation, ADC_CFG1[ADLPC] must be set, the ADC_CFG2[ADHSC] bit must be clear with 1 MHz ADC conversion clock speed.
- 4. $1 LSB = (V_{REFH} V_{REFL})/2^{N}$
- 5. ADC conversion clock < 16 MHz, Max hardware averaging (AVGE = %1, AVGS = %11)
- 6. VREFH = Output of Voltage Reference(VREF)
- 7. Input data is 100 Hz sine wave. ADC conversion clock < 12 MHz.
- 8. ADC conversion clock < 3 MHz

7.5.6.2 Voltage reference electrical specifications

Table 33. VREF full-range operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
V_{DDA}	Supply voltage	1.71	3.6	V	
T _A	Temperature	-40 to 105		°C	
C _L	Output load capacitance	100		nF	1, 2

- 1. C_L must be connected to VREF_OUT if the VREF_OUT functionality is being used for either an internal or external reference.
- 2. The load capacitance should not exceed +/-25% of the nominal specified C_L value over the operating temperature range of the device.

Table 34. VREF full-range operating behaviors

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
V _{out}	Voltage reference output with factory trim at nominal V _{DDA} and temperature=25°C	1.190	1.1950	1.2	V	1
V _{out}	Voltage reference output with user trim at nominal V _{DDA} and temperature=25°C	1.1945	1.1950	1.1955	V	1
V _{step}	Voltage reference trim step	_	0.5	_	mV	1

Table 34. VREF full-range operating behaviors (continued)

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
V _{tdrift}	Temperature drift (Vmax -Vmin across the full temperature range)	_	_	20	mV	1
I _{bg}	Bandgap only current	_	_	80	μΑ	
I _{Ip}	Low-power buffer current	_	_	360	uA	1
I _{hp}	High-power buffer current	_	_	1	mA	1
ΔV_{LOAD}	Load regulation				μV	1, 2
	• current = ± 1.0 mA	_	200	_		
T _{stup}	Buffer startup time	_	_	100	μs	
T _{chop_osc_st}	Internal bandgap start-up delay with chop oscillator enabled	_	_	35	ms	
V _{vdrift}	Voltage drift (Vmax -Vmin across the full voltage range)	_	2	_	mV	1

^{1.} See the chip's Reference Manual for the appropriate settings of the VREF Status and Control register.

Table 35. VREF limited-range operating requirements

	Symbol	Description	Min.	Max.	Unit	Notes
Ī	T_A	Temperature	0	70	°C	

Table 36. VREF limited-range operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
V _{tdrift}	Temperature drift (V _{max} -V _{min} across the limited temperature range)	_	15	mV	

7.5.6.3 CMP and 6-bit DAC electrical specifications Table 37. Comparator and 6-bit DAC electrical specifications

Symbol	Description	Min.	Тур.	Max.	Unit
V_{DD}	Supply voltage	1.71	_	3.6	V
I _{DDHS}	Supply current, High-speed mode (EN=1, PMODE=1)	_	_	200	μA
I _{DDLS}	Supply current, low-speed mode (EN=1, PMODE=0)	_	_	20	μΑ
V _{AIN}	Analog input voltage	V _{SS} - 0.3	_	V_{DD}	V
V _{AIO}	Analog input offset voltage	_	_	20	mV
V _H	Analog comparator hysteresis ¹				
	• CR0[HYSTCTR] = 00	_	5	_	mV

^{2.} Load regulation voltage is the difference between the VREF_OUT voltage with no load vs. voltage with defined load

Symbol	Description	Min.	Тур.	Max.	Unit
	• CR0[HYSTCTR] = 01	_	10	_	mV
	CR0[HYSTCTR] = 10	_	20	_	mV
	CR0[HYSTCTR] = 11	_	30	_	mV
V _{CMPOh}	Output high	V _{DD} – 0.5	_	_	V
V _{CMPOI}	Output low	_	_	0.5	V
t _{DHS}	Propagation delay, high-speed mode (EN=1, PMODE=1)	20	50	200	ns
t _{DLS}	Propagation delay, low-speed mode (EN=1, PMODE=0)	80	250	600	ns
	Analog comparator initialization delay ²	_	_	40	μs
I _{DAC6b}	6-bit DAC current adder (enabled)	_	7	_	μA
INL	6-bit DAC integral non-linearity	-0.5	_	0.5	LSB ³
DNL	6-bit DAC differential non-linearity	-0.3	_	0.3	LSB

- 1. Typical hysteresis is measured with input voltage range limited to 0.6 to V_{DD} -0.6 V.
- Comparator initialization delay is defined as the time between software writes to change control inputs (Writes to CMP_DACCR[DACEN], CMP_DACCR[VRSEL], CMP_DACCR[VOSEL], CMP_MUXCR[PSEL], and CMP_MUXCR[MSEL]) and the comparator output settling to a stable level.
- 3. $1 LSB = V_{reference}/64$

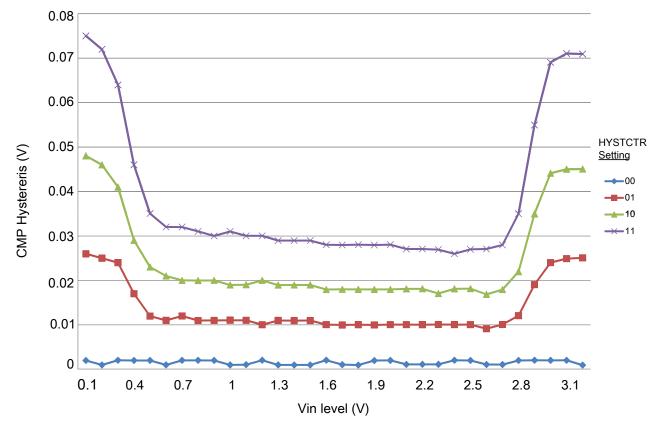


Figure 9. Typical hysteresis vs. Vin level (VDD = 3.3 V, PMODE = 0)

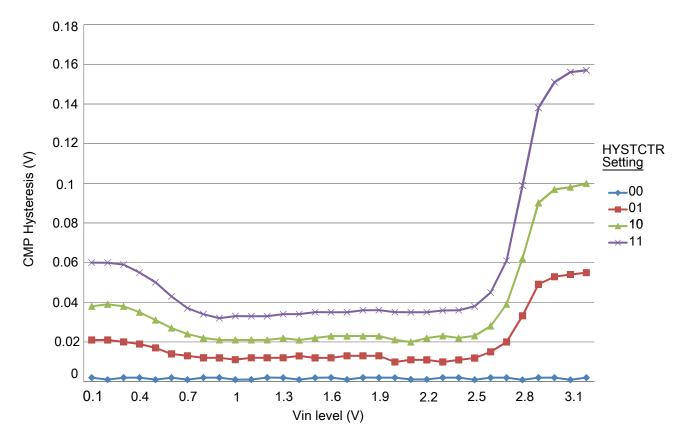


Figure 10. Typical hysteresis vs. Vin level (VDD = 3.3 V, PMODE = 1)

7.5.6.4 12-bit DAC electrical characteristics

7.5.6.4.1 12-bit DAC operating requirements Table 38. 12-bit DAC operating requirements

Symbol	Desciption	Min.	Max.	Unit	Notes
V_{DDA}	Supply voltage	1.71	3.6	V	
V _{DACR}	Reference voltage	1.13	3.6	V	1
C _L	Output load capacitance	_	100	pF	2
IL	Output load current	_	1	mA	

^{1.} The DAC reference can be selected to be V_{DDA} or V_{REFH} .

^{2.} A small load capacitance (47 pF) can improve the bandwidth performance of the DAC.

7.5.6.4.2 12-bit DAC operating behaviors Table 39. 12-bit DAC operating behaviors

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
I _{DDA_DACL}	Supply current — low-power mode	_	_	250	μΑ	
I _{DDA_DACH}	Supply current — high-speed mode	_	_	900	μΑ	
t _{DACLP}	Full-scale settling time (0x080 to 0xF7F) — low-power mode	_	100	200	μs	1
t _{DACHP}	Full-scale settling time (0x080 to 0xF7F) — high-power mode	_	15	30	μs	1
t _{CCDACLP}	Code-to-code settling time (0xBF8 to 0xC08) — low-power mode and high-speed mode	_	0.7	1	μs	1
V _{dacoutl}	DAC output voltage range low — high- speed mode, no load, DAC set to 0x000	_	_	100	mV	
V _{dacouth}	DAC output voltage range high — high- speed mode, no load, DAC set to 0xFFF	V _{DACR} -100	_	V_{DACR}	mV	
INL	Integral non-linearity error — high speed mode	_	_	±8	LSB	2
DNL	Differential non-linearity error — V _{DACR} > 2 V	_	_	±1	LSB	3
DNL	Differential non-linearity error — V _{DACR} = VREF_OUT	_	_	±1	LSB	4
V _{OFFSET}	Offset error	_	±0.4	±0.8	%FSR	5
E _G	Gain error	_	±0.1	±0.6	%FSR	5
PSRR	Power supply rejection ratio, V _{DDA} ≥ 2.4 V	60	_	90	dB	
T_CO	Temperature coefficient offset voltage	_	3.7	_	μV/C	6
T_GE	Temperature coefficient gain error	_	0.000421	_	%FSR/C	
Rop	Output resistance (load = $3 \text{ k}\Omega$)	_	_	250	Ω	
SR	Slew rate -80h→ F7Fh→ 80h				V/µs	
	High power (SP _{HP})	1.2	1.7	-		
	Low power (SP _{LP})	0.05	0.12	_		
BW	3dB bandwidth				kHz	
	High power (SP _{HP})	550	_	_		
	Low power (SP _{LP})	40	_	_		

- 1. Settling within ±1 LSB
- 2. The INL is measured for 0 + 100 mV to V_{DACR} –100 mV
- 3. The DNL is measured for 0 + 100 mV to V_{DACR} -100 mV 4. The DNL is measured for 0 + 100 mV to V_{DACR} -100 mV with V_{DDA} > 2.4 V 5. Calculated by a best fit curve from V_{SS} + 100 mV to V_{DACR} 100 mV
- 6. $V_{DDA} = 3.0 \text{ V}$, reference select set for V_{DDA} (DACx_CO:DACRFS = 1), high power mode (DACx_CO:LPEN = 0), DAC set to 0x800, temperature range is across the full range of the device

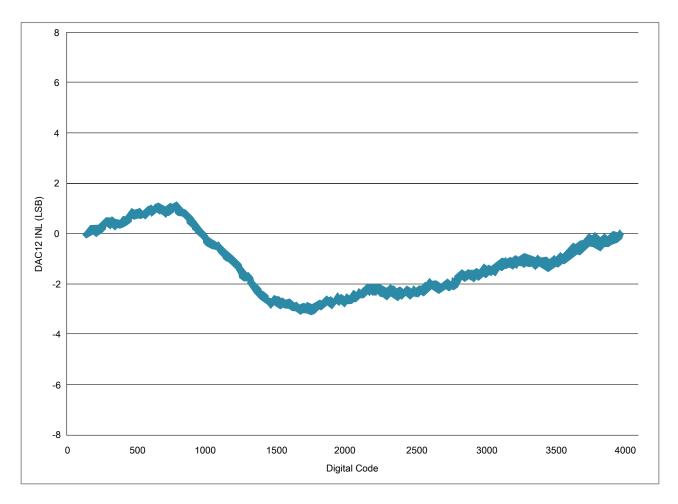


Figure 11. Typical INL error vs. digital code

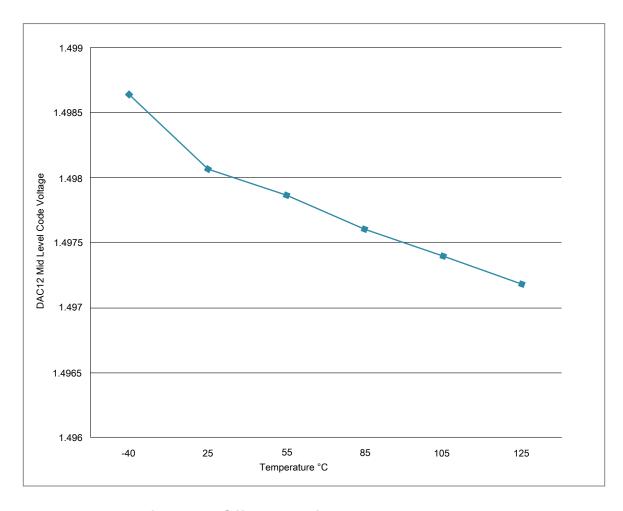


Figure 12. Offset at half scale vs. temperature

7.5.7 Timers

See General switching specifications.

7.5.8 Communication interfaces

7.5.8.1 DSPI switching specifications (limited voltage range)

The DMA Serial Peripheral Interface (DSPI) provides a synchronous serial bus with master and slave operations. Many of the transfer attributes are programmable. The tables below provide DSPI timing characteristics for classic SPI timing modes. Refer to the DSPI chapter of the Reference Manual for information on the modified transfer formats used for communicating with slower peripheral devices.

Num	Description	Min.	Max.	Unit	Notes
	Operating voltage	2.7	3.6	V	
	Frequency of operation	_	12	MHz	
DS1	DSPI_SCK output cycle time	2 x t _{BUS}	_	ns	
DS2	DSPI_SCK output high/low time	(t _{SCK} /2) - 2	(t _{SCK} /2) + 2	ns	
DS3	DSPI_PCSn valid to DSPI_SCK delay	(t _{BUS} x 2) –	_	ns	1
DS4	DSPI_SCK to DSPI_PCSn invalid delay	(t _{BUS} x 2) –	_	ns	2
DS5	DSPI_SCK to DSPI_SOUT valid	_	8.5	ns	
DS6	DSPI_SCK to DSPI_SOUT invalid	-2	_	ns	
DS7	DSPI_SIN to DSPI_SCK input setup	16.2	_	ns	
DS8	DSPL SCK to DSPL SIN input hold	0	_	ns	

Table 40. Master mode DSPI timing (limited voltage range)

- 1. The delay is programmable in SPIx_CTARn[PSSCK] and SPIx_CTARn[CSSCK].
- 2. The delay is programmable in SPIx_CTARn[PASC] and SPIx_CTARn[ASC].

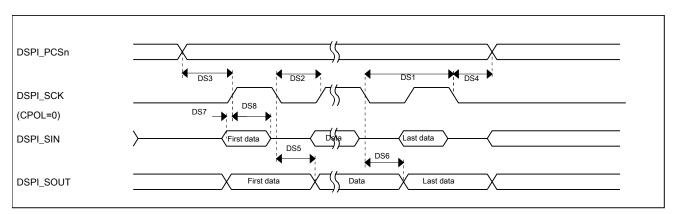


Figure 13. DSPI classic SPI timing — master mode

Table 41. Slave mode DSPI timing (limited voltage range)

Num	Description	Min.	Max.	Unit
	Operating voltage	2.7	3.6	V
	Frequency of operation		6	MHz

Num	Description	Min.	Max.	Unit
DS9	DSPI_SCK input cycle time	4 x t _{BUS}	_	ns
DS10	DSPI_SCK input high/low time	(t _{SCK} /2) - 2	(t _{SCK} /2) + 2	ns
DS11	DSPI_SCK to DSPI_SOUT valid	_	21.4	ns
DS12	DSPI_SCK to DSPI_SOUT invalid	0	_	ns
DS13	DSPI_SIN to DSPI_SCK input setup	2.6	_	ns
DS14	DSPI_SCK to DSPI_SIN input hold	7.0	_	ns
DS15	DSPI_SS active to DSPI_SOUT driven	_	14	ns
DS16	DSPI_SS inactive to DSPI_SOUT not driven	_	14	ns

Table 41. Slave mode DSPI timing (limited voltage range) (continued)

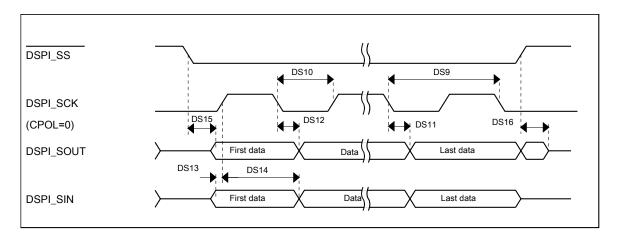


Figure 14. DSPI classic SPI timing — slave mode

7.5.8.2 DSPI switching specifications (full voltage range)

The DMA Serial Peripheral Interface (DSPI) provides a synchronous serial bus with master and slave operations. Many of the transfer attributes are programmable. The tables below provides DSPI timing characteristics for classic SPI timing modes. Refer to the DSPI chapter of the Reference Manual for information on the modified transfer formats used for communicating with slower peripheral devices.

Max. Num Description Min. Unit **Notes** Operating voltage 1.71 3.6 V 1 12 Frequency of operation MHz DS₁ DSPI_SCK output cycle time 2 x t_{BUS} ns DS₂ DSPI_SCK output high/low time $(t_{SCK}/2) - 4$ $(t_{SCK/2}) + 4$ ns

Table 42. Master mode DSPI timing (full voltage range)

Num	Description	Min.	Max.	Unit	Notes
DS3	DSPI_PCSn valid to DSPI_SCK delay	(t _{BUS} x 2) –	_	ns	2
DS4	DSPI_SCK to DSPI_PCSn invalid delay	(t _{BUS} x 2) – 4	_	ns	3
DS5	DSPI_SCK to DSPI_SOUT valid	_	10	ns	
DS6	DSPI_SCK to DSPI_SOUT invalid	-1.2	_	ns	
DS7	DSPI_SIN to DSPI_SCK input setup	23.3	_	ns	
DS8	DSPI_SCK to DSPI_SIN input hold	0	_	ns	

- 1. The DSPI module can operate across the entire operating voltage for the processor, but to run across the full voltage range the maximum frequency of operation is reduced.
- 2. The delay is programmable in SPIx_CTARn[PSSCK] and SPIx_CTARn[CSSCK].
- 3. The delay is programmable in SPIx_CTARn[PASC] and SPIx_CTARn[ASC].

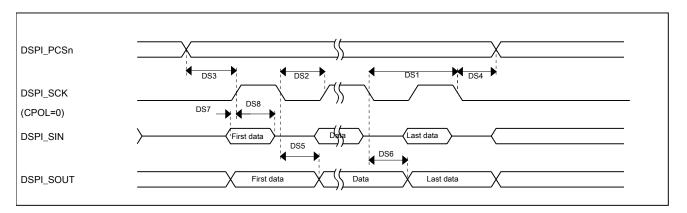


Figure 15. DSPI classic SPI timing — master mode

Table 43. Slave mode DSPI timing (full voltage range)

Num	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
	Frequency of operation	_	6	MHz
DS9	DSPI_SCK input cycle time	4 x t _{BUS}	_	ns
DS10	DSPI_SCK input high/low time	(t _{SCK} /2) - 4	(t _{SCK/2)} + 4	ns
DS11	DSPI_SCK to DSPI_SOUT valid	_	29.1	ns
DS12	DSPI_SCK to DSPI_SOUT invalid	0	_	ns
DS13	DSPI_SIN to DSPI_SCK input setup	3.2	_	ns
DS14	DSPI_SCK to DSPI_SIN input hold	7.0	_	ns
DS15	DSPI_SS active to DSPI_SOUT driven	_	25	ns
DS16	DSPI_SS inactive to DSPI_SOUT not driven	_	25	ns

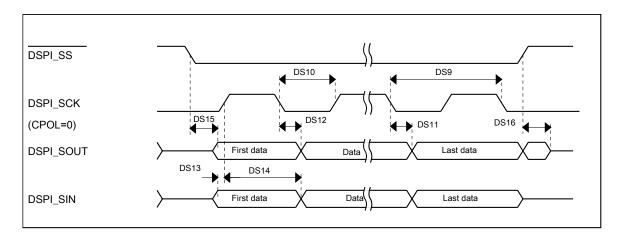


Figure 16. DSPI classic SPI timing — slave mode

7.5.8.3 Inter-Integrated Circuit Interface (I²C) timing Table 44. I ²C timing

Characteristic	Symbol	Standard Mode		Fast Mode		Standard Mode Fast Mode		Unit
		Minimum	Maximum	Minimum	Maximum			
SCL Clock Frequency	f _{SCL}	0	100	0	400	kHz		
Hold time (repeated) START condition. After this period, the first clock pulse is generated.	t _{HD} ; STA	4	_	0.6	_	μs		
LOW period of the SCL clock	t_{LOW}	4.7	_	1.3	_	μs		
HIGH period of the SCL clock	t _{HIGH}	4	_	0.6	_	μs		
Set-up time for a repeated START condition	t _{SU} ; STA	4.7	_	0.6	_	μs		
Data hold time for I ² C bus devices	t _{HD} ; DAT	O ¹	3.45 ²	0 ³	0.9 ¹	μs		
Data set-up time	t _{SU} ; DAT	250 ⁴	_	100 ^{2, 5}	_	ns		
Rise time of SDA and SCL signals	t _r	_	1000	20 +0.1C _b ⁶	300	ns		
Fall time of SDA and SCL signals	t _f	_	300	20 +0.1C _b ⁵	300	ns		
Set-up time for STOP condition	t _{SU} ; STO	4	_	0.6	_	μs		
Bus free time between STOP and START condition	t _{BUF}	4.7	_	1.3	_	μs		
Pulse width of spikes that must be suppressed by the input filter	t _{SP}	N/A	N/A	0	50	ns		

- 1. The master mode I²C deasserts ACK of an address byte simultaneously with the falling edge of SCL. If no slaves acknowledge this address byte, then a negative hold time can result, depending on the edge rates of the SDA and SCL lines.
- 2. The maximum tHD; DAT must be met only if the device does not stretch the LOW period (tLOW) of the SCL signal.
- 3. Input signal Slew = 10 ns and Output Load = 50 pF
- 4. Set-up time in slave-transmitter mode is 1 IPBus clock period, if the TX FIFO is empty.
- 5. A Fast mode I²C bus device can be used in a Standard mode I2C bus system, but the requirement $t_{SU; DAT} \ge 250$ ns must then be met. This is automatically the case if the device does not stretch the LOW period of the SCL signal. If such a device does stretch the LOW period of the SCL signal, then it must output the next data bit to the SDA line t_{max}

- + t_{SU; DAT} = 1000 + 250 = 1250 ns (according to the Standard mode I²C bus specification) before the SCL line is released.
- 6. $C_b = total$ capacitance of the one bus line in pF.

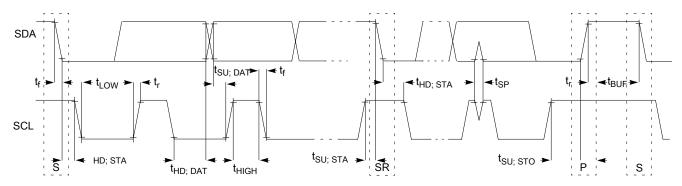


Figure 17. Timing definition for fast and standard mode devices on the I²C bus

7.5.8.4 LPUART

See General switching specifications.

7.5.9 Human-machine interfaces (HMI)

7.5.9.1 TSI electrical specifications Table 45. TSI electrical specifications

Symbol	Description	Min.	Тур.	Max.	Unit
Та	Temperature	-30	_	105	°C
TSI_RUNF	Fixed power consumption in run mode	_	100	_	μA
TSI_RUNV	TSI_RUNV Variable power consumption in run mode (depends on oscillator's current selection)		_	128	μА
TSI_EN	Power consumption in enable mode	_	100	_	μA
TSI_DIS	TSI_DIS Power consumption in disable mode		1.2	_	μA
TSI_TEN TSI analog enable time		_	66	_	μs
TSI_CREF	SI_CREF TSI reference capacitor		1.0	_	pF
TSI_DVOLT	Voltage variation of VP & VM around nominal values	0.19	_	1.03	V

7.5.9.2 GPIO

The maximum input voltage on PTC0/1/2/3 is VDD+0.3V. For rest of the GPIO specification, see General switching specifications.

8 KW41Z Electrical Characteristics

8.1 DC-DC Converter Recommended Electrical Characteristics

Table 46. DC-DC Converter Recommended operating conditions

Characteristic	Symbol	Min	Тур	Max	Unit
Bypass Mode Supply Voltage (RF and Analog)	VDD _{RF1} , VDD _{RF2} , VDD _{RF3}	1.425	_	3.6	Vdc
Bypass Mode Supply Voltage (Digital)	$VDD_X, V_{DCDC_IN}, VDD_A$	1.71	_	3.6	Vdc
Boost Mode Supply Voltage	VDD _{DCDC_IN}	0.9	_	1.795	Vdc
Buck Mode Supply Voltage ^{2, 1}	VDD _{DCDC_IN}	2.1	_	4.2	Vdc

In Buck and Boost modes, DC-DC converter will generate 1.8V at VDD_1P8OUT and 1.5V at VDD_1P5OUT_PMCIN pins. VDD_1P8OUT should supply to VDD₁, VDD₂ and VDD_A. VDD_1P5OUT_PMCIN should supply to VDD_RF₁ and VDD_RF₂. VDD_{XTAL} can be either supplied by 1.5V or 1.8V

Table 47. DC-DC Converter Specifications

Characteristics	Conditions	Symbol	Min	Тур	Max	Unit
DC-DC Converter Output Power	Total power output of 1p8V and 1p5V	Pdcdc_out	-	-	125 ¹	mW
Boost Mode						
DO DO Octobrida los diVellassa	Operating Voltage Range	VDCDC_IN_boost	0.9	-	1.795	Vdc
DC-DC Converter Input Voltage	DC-DC Startup Voltage Range ²	VDCDC_IN_boost _startup	1.1	-	-	Vdc
1.8V Output Voltage		VDD_1P8_boost	-	1.8 ³	3	Vdc
	VDD_1P8 = 1.8V, VDCDC_IN = 1.7V	IDD_1P8_boost1	-	-	45	mA
1.8V Output Current ^{4, 5}	VDD_1P8 = 3.0V, VDCDC_IN = 1.7V	IDD_1P8_boost2	-	-	27	mA
	VDD_1P8 = 1.8V, VDCDC_IN = 0.9V	IDD_1P8_boost3	-	-	20	mA

^{2.} In Buck mode, DC-DC converter needs 2.1V min to start, the supply can drop to 1.8V after DC-DC converter settles

Table 47.	DC-DC Converter	Specifications	(continued)	
-----------	------------------------	-----------------------	-------------	--

Characteristics	Conditions	Symbol	Min	Тур	Max	Unit
	VDD_1P8 = 3.0V, VDCDC_IN = 0.9V	IDD_1P8_boost4	-	-	10	mA
1.5V Output Voltage		VDD_1P5_boost	-	1.8 ^{6, 7}	2.0	Vdc
1.5V Output Current ^{4, 8}		VDD_1P5_boost	-	-	30	mA
Buck Mode						
DC DC Converter Input Veltage	Operating Voltage Range	VDCDC_IN_buck	1.8	-	4.2	Vdc
DC-DC Converter Input Voltage	DC-DC Startup Voltage Range ⁹	VDCDC_IN_buck _startup	2.1	-	-	Vdc
1.8V Output Voltage		VDD_1P8_buck	1.71	-	min(VDCD C_IN_buc k, 3) ^{10, 3}	Vdc
1.8V Output Current ^{4, 5}	VDD_1P8 = 1.8V, VDC_1P5 = 1.5V	IDD_1P8_buck1	-	-	45	mA
1.6V Output Guilent	VDD_1P8 = 3.0V, VDC_1P5 = 1.5V	IDD_1P8_buck2	-	-	27	mA
1.5V Output Voltage	Radio section requires 1.5V	VDD_1P5_buck	-	1.5 ¹¹	2.0	Vdc
1.5V Output Current ^{4, 8}		IDD_1P5_buck	-	-	30	mA

- 1. This is the steady state DC output power. It requires VDCDC_IN >= 1.7V in boost mode. Excessive transient current load from external device will cause 1p8V and 1P5 output voltage unregulated temporary.
- 2. DC-DC converter requires slightly higher input voltage during startup. VDCDC_IN_boost_startup is the minimum startup voltages for the DC-DC converter in boost mode. Bit DCDC_STS_DC_OK will be set when the DC-DC converter finish the startup sequence. Typical startup time is 50ms and it varies with the loading of the converter.
- 3. The voltage output level can be controlled by programming DCDC_VDD1P8CTRL_TRG field in DCDC_REG3.
- 4. The output current specification in both buck and boost modes represents the maximum current the DC-DC converter can deliver. The KW41Z radio and MCU blocks current consumption is not excluded. Note that the maximum output power of the DC-DC converter is 125mW. The available supply current for external device depends on the energy consumed by the internal peripherals in KW41Z.
- 5. When using DC-DC in low power mode(pulsed mode), current load must be less than 1mA.
- 6. In Boost mode, the minimum 1.5V output is the maximum of either what is programmed using DCDC_VDD1P5CTRL_TRG_BOOST field in DCDC_REG3 or VDCDC_IN_boost + 0.05V. For example, if VDCDC_IN = 0.9V, minimum VDD_1P5 is as programmed in DCDC_VDD1P5CTRL_TRG_BOOST. If VDCDC_IN = 1.5V, minimum VDD_1P5 = 1.5 + 0.05V is 1.55V.
- 1.8V is default value of the DC-DC 1.5V output voltage in boost mode. The user can program DCDC_VDD1P5CTRL_TRG_BOOST field in register DCDC_REG3 to control 1.5V output voltage level. For reliable radio operation, a voltage level of 1.425V is required.
- 8. 1.5V is intended to supply power to KW41Z only. It is not designed to supply power to an external device.
- 9. DC-DC converter requires slightly higher input voltage during startup. VDCDC_IN_buck_startup is the minimum startup voltages for the DC-DC converter in buck mode. Bit DCDC_STS_DC_OK will be set when the DC-DC converter finish the startup sequence. Typical startup time is 50ms and it varies with the loading of the converter.
- 10. In Buck mode, the maximum 1.8V output is the minimum of either VDCDC_IN_BUCK or 3V. For example, if VDCDC_IN = 1.8V, maximum VDD_1P8 is 1.8V. If VDCDC_IN = 4.2V, maximum VDD_1P8 is 3V.
- 11. User needs to program DCDC_VDD1P5CTRL_TRG_BUCK field in DCDC_REG3 register to ensure that a worst case minimum of 1.425V is available as VDD_1P5_buck for radio operation.

8.2 Ratings

8.2.1 Thermal handling ratings

Table 48. Thermal handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
T _{STG}	Storage temperature	- 55	150	°C	1
T _{SDR}	Solder temperature, lead-free	_	260	°C	2

- 1. Determined according to JEDEC Standard JESD22-A103, High Temperature Storage Life.
- Determined according to IPC/JEDEC Standard J-STD-020, Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices.

8.2.2 Moisture handling ratings

Table 49. Moisture handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
MSL	Moisture sensitivity level	_	3	_	1

1. Determined according to IPC/JEDEC Standard J-STD-020, Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices.

8.2.3 ESD handling ratings

Table 50. ESD handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
V _{HBM}	Electrostatic discharge voltage, human body model	-2000	+2000	V	1
V _{CDM}	Electrostatic discharge voltage, charged-device model	-500	+500	V	2
I _{LAT}	Latch-up current at ambient temperature of 105 °C	-100	+100	mA	3

- 1. Determined according to JEDEC Standard JESD22-A114, *Electrostatic Discharge (ESD) Sensitivity Testing Human Body Model (HBM)*.
- 2. Determined according to JEDEC Standard JESD22-C101, Field-Induced Charged-Device Model Test Method for Electrostatic-Discharge-Withstand Thresholds of Microelectronic Components.
- 3. Determined according to JEDEC Standard JESD78, IC Latch-Up Test.

8.2.4 Voltage and current operating ratings

Table 51. Voltage and current operating ratings

Symbol	Description	Min.	Max.	Unit
V_{DD}	Digital supply voltage	-0.3	3.8	V
I _{DD}	Digital supply current	_	120	mA
V _{IO}	IO pin input voltage	-0.3	V _{DD} + 0.3	V
I _D	I _D Instantaneous maximum current single pin limit (applies to all port pins)		25	mA
V_{DDA}	Analog supply voltage	V _{DD} – 0.3	V _{DD} + 0.3	V

9 Pin Diagrams and Pin Assignments

9.1 Pinouts

Device pinout are shown in figures below.

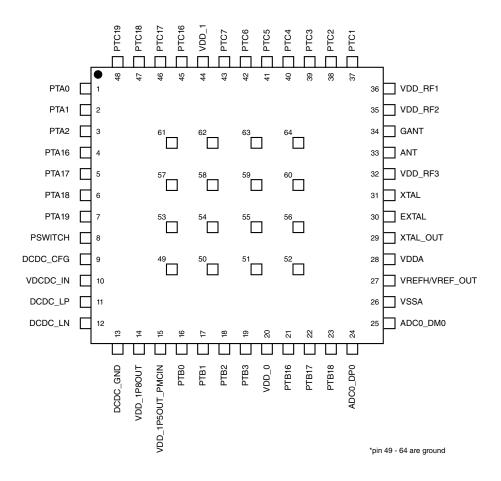


Figure 18. 48-pin Laminate QFN pinout diagram

9.2 Signal Multiplexing and Pin Assignments

The following table shows the signals available on each pin and locations of these pins on the packages supported by this device. The Port Control Module is responsible for selecting which ALT functional is available on each PTxy pin.

Table 52. KW41Z Pin Assignments

KW41Z(48 LGA / Laminat e QFN)	Pin Name	DEFAUL T	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7
1	PTA0	SWD_DI O	TSIO_CH 8	PTA0	SPI0_PC S1			TPM1_C H0		SWD_DI O
2	PTA1	SWD_CL K	TSI0_CH 9	PTA1	SPI1_PC S0			TPM1_C H1		SWD_CL K

Table 52. KW41Z Pin Assignments (continued)

KW41Z(48 LGA / Laminat e QFN)	Pin Name	DEFAUL T	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7
3	PTA2	RESET_ b		PTA2				TPM0_C H3		RESET_ b
4	PTA16	DISABLE D	TSI0_CH 10	PTA16/ LLWU_P 4	SPI1_SO UT			TPM0_C H0		
5	PTA17	DISABLE D	TSI0_CH 11	PTA17/ LLWU_P 5/ RF_RES ET	SPI1_SIN			TPM_CL KIN1		
6	PTA18	DISABLE D	TSI0_CH 12	PTA18/ LLWU_P 6	SPI1_SC K			TPM2_C H0		
7	PTA19	DISABLE D	TSI0_CH 13/ ADC0_S E5	PTA19/ LLWU_P 7	SPI1_PC S0			TPM2_C H1		
8	PSWITC H	PSWITC H	PSWITC H							
9	DCDC_C FG	DCDC_C FG	DCDC_C FG							
10	VDCDC_I N	VDCDC_I N	VDCDC_I N							
11	DCDC_L P	DCDC_L P	DCDC_L P							
12	DCDC_L N	DCDC_L N	DCDC_L N							
13	DCDC_G ND	DCDC_G ND	DCDC_G ND							
14	VDD_1P 8OUT	VDD_1P 8OUT	VDD_1P 8OUT							
15	VDD_1P 5OUT_P MCIN	VDD_1P 5OUT_P MCIN	VDD_1P 5OUT_P MCIN							
16	РТВ0	DISABLE D		PTB0/ LLWU_P 8/ XTAL_O UT_EN		12C0_SC L	CMP0_O UT	TPM0_C H1		CLKOUT
17	PTB1	DISABLE D	ADC0_S E1/ CMP0_IN 5	PTB1	DTM_RX	I2C0_SD A	LPTMR0 _ALT1	TPM0_C H2		CMT_IR O

Table 52. KW41Z Pin Assignments (continued)

KW41Z(Pin	DEFAUL	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7
48 LGA / Laminat e QFN)	Name	Т								
18	PTB2	DISABLE D	ADC0_S E3/ CMP0_IN 3	PTB2	RF_NOT _ALLOW ED	DTM_TX		TPM1_C H0		
19	PTB3	DISABLE D	ADC0_S E2/ CMP0_IN 4	РТВ3			CLKOUT	TPM1_C H1		RTC_CL KOUT
20	VDD_0	VDD_0	VDD_0							
21	PTB16	EXTAL32 K	EXTAL32 K	PTB16		I2C1_SC L		TPM2_C H0		
22	PTB17	XTAL32K	XTAL32K	PTB17		I2C1_SD A		TPM2_C H1		BSM_CL K
23	PTB18	NMI_b	DACO_O UT/ ADCO_S E4/ CMPO_IN 2	PTB18		I2C1_SC L	TPM_CL KIN0	TPM0_C H0		NMI_b
24	ADC0_D P0	ADC0_D P0/ CMP0_IN 0	ADC0_D P0/ CMP0_IN 0							
25	ADC0_D M0	ADC0_D M0/ CMP0_IN 1	ADC0_D M0/ CMP0_IN 1							
26	VSSA	VSSA	VSSA							
27	VREFH/ VREF_O UT	VREFH/ VREF_O UT	VREFH/ VREF_O UT							
28	VDDA	VDDA	VDDA							
29	XTAL_O UT	XTAL_O UT	XTAL_O UT							
30	EXTAL	EXTAL	EXTAL							
31	XTAL	XTAL	XTAL							
32	VDD_RF 3	VDD_RF 3	VDD_RF 3							
33	ANT	ANT	ANT							
34	GANT	GANT	GANT							
35	VDD_RF 2	VDD_RF 2	VDD_RF 2							

Table 52. KW41Z Pin Assignments (continued)

KW41Z(Pin	DEFAUL	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7
48 LGA / Laminat e QFN)	Name	Т								
36	VDD_RF 1	VDD_RF 1	VDD_RF 1							
37	PTC1	DISABLE D		PTC1	ANT_B	I2C0_SD A	LPUART 0_RTS_b	TPM0_C H2		BLE_RF_ ACTIVE
38	PTC2	DISABLE D	TSI0_CH 14/DIAG1		TX_SWIT CH	I2C1_SC L	LPUART 0_RX	CMT_IR O		DTM_RX
39	PTC3	DISABLE D	TSI0_CH 15/DIAG2		RX_SWI TCH	I2C1_SD A	LPUART 0_TX	TPM0_C H1		DTM_TX
40	PTC4	DISABLE D	TSI0_CH 0/DIAG3	PTC4/ LLWU_P 12	ANT_A	EXTRG_I N	LPUART 0_CTS_b	TPM1_C H0		BSM_DA TA
41	PTC5	DISABLE D	TSI0_CH 1/DIAG4	PTC5/ LLWU_P 13	RF_NOT _ALLOW ED	LPTMR0 _ALT2	LPUART 0_RTS_b	TPM1_C H1		BSM_CL K
42	PTC6	DISABLE D	TSI0_CH 2	PTC6/ LLWU_P 14/ XTAL_O UT_EN		I2C1_SC L	LPUART 0_RX	TPM2_C H0		BSM_FR AME
43	PTC7	DISABLE D	TSI0_CH 3	PTC7/ LLWU_P 15	SPI0_PC S2	I2C1_SD A	LPUART 0_TX	TPM2_C H1		BSM_DA TA
44	VDD_1	VDD_1	VDD_1							
45	PTC16	DISABLE D	TSI0_CH 4	PTC16/ LLWU_P 0	SPI0_SC K	I2C0_SD A	LPUART 0_RTS_b	TPM0_C H3		
46	PTC17	DISABLE D	TSI0_CH 5	PTC17/ LLWU_P 1	SPI0_SO UT	I2C1_SC L	LPUART 0_RX	BSM_FR AME		DTM_RX
47	PTC18	DISABLE D	TSI0_CH 6	PTC18/ LLWU_P 2	SPI0_SIN	I2C1_SD A	LPUART 0_TX	BSM_DA TA		DTM_TX
48	PTC19	DISABLE D	TSI0_CH 7	PTC19/ LLWU_P 3	SPI0_PC S0	I2C0_SC L	LPUART 0_CTS_b	BSM_CL K		BLE_RF_ ACTIVE
49-64	Ground	NA								

9.3 Module Signal Description Tables

The following sections correlate the chip-level signal name with the signal name used in the module's chapter. They also briefly describe the signal function and direction.

9.3.1 Core Modules

This section contains tables describing the core module signal descriptions.

Table 53. SWD Module Signal Descriptions

SoC Signal Name	Module Signal Name	Description	I/O
SWD_DIO	SWD_DIO	Serial Wire Debug Data Input/Output ¹	I/O
SWD_CLK	SWD_CLK	Serial Wire Clock ²	

- 1. Pulled up internally by default
- 2. Pulled down internally by default

9.3.2 Radio Modules

This section contains tables describing the radio signals.

Table 54. Radio Module Signal Descriptions

SoC Signal Name	Module Signal Name	Description	I/O
ANT	ANT	Antenna	0
GANT	GANT	Antenna ground	I
BLE_RF_ACTIVE	BLE_RF_ACTIVE	Signal to indicate future BLE activity. Refer BLE Link Layer for more details.	0
RF_NOT_ALLOWED	RF_NOT_ALLOWED	Radio off signal, intended for WiFi coexistence control	I
RF_RESET	RF_RESET	Radio reset signal	I
DTM_RX	DTM_RX	Direct Test Mode Receive	I
DTM_TX	DTM_TX	Direct Test Mode Transmit	0
BSM_CLK	BSM_CLK	Bit Streaming Mode (BSM) Clock signal, 802.15.4 packet data stream clock line	0
BSM_FRAME	BSM_FRAME	Bit Streaming Mode Frame signal, 802.15.4 packet data stream frame line	0

Table 54. Radio Module Signal Descriptions (continued)

SoC Signal Name	Module Signal Name	Description	I/O
BSM_DATA	BSM_DATA	Bit Streaming Mode Data signal, 802.15.4 packet data stream data line	I/O
ANT_A	ANT_A	Antenna selection A for Front End Module support	0
ANT_B	ANT_B	Antenna selection B for Front End Module support	0
TX_SWITCH	TX_SWITCH	Front End Module Transmit mode signal	0
RX_SWITCH	RX_SWITCH	Front End Module Receive mode signal	0

9.3.3 System Modules

This section contains tables describing the system signals.

Table 55. System Module Signal Descriptions

SoC Signal Name	Module Signal Name	Description	I/O
NMI_b	_	Non-maskable interrupt	I
RESET_b	_	Reset bidirectional signal	I/O
VDD_[1:0]	VDD	Power supply	I
Ground	VSS	Ground	I
VDD_RF[3:1]	VDD_RF	Radio power supply	I
VDCDC_IN	VDCDC_IN	VDCDC_IN	I
VDD_1P8OUT	VDD_1P8	DCDC 1.8 V Regulated Output / Input in bypass	I/O
VDD_1P5OUT_PMCIN	VDD_1P5/VDD_PMC	DCDC 1.5 V Regulated Output / PMC Input in bypass	I/O
PSWITCH	PSWITCH	DCDC enable switch	I
DCDC_CFG	DCDC_CFG	DCDC switch mode select	I
DCDC_LP	DCDC_LP	DCDC inductor input positive	I/O
DCDC_LN	DCDC_LN	DCDC inductor input negative	I/O
DCDC_GND	DCDC_GND	DCDC ground	I

Table 56. LLWU Module Signal Descriptions

SoC Signal Name	Module Signal Name	Description	I/O
LLWU_P[15:0]	LLWU_P[15:0]	Wakeup inputs	

9.3.4 Clock Modules

This section contains tables for Clock signal descriptions.

Table 57. Clock Module Signal Descriptions

SoC Signal Name	Module Signal Name	Description	I/O
EXTAL	EXTAL	26 MHz/32 MHz External clock/Oscillator input	I
XTAL	XTAL	26 MHz/32 MHz Oscillator input	I
XTAL_OUT	XTAL_OUT	26 MHz/32 MHz Clock output	0
XTAL_OUT_EN	XTAL_OUT_ENABLE	26 MHz/32 MHz Clock output enable for XTAL_OUT	I
EXTAL32K	EXTAL32K	32 kHz External clock/ Oscillator input	I
XTAL32K	XTAL32K	32 kHz Oscillator input	I
CLKOUT	CLKOUT	Internal clocks monitor	0

9.3.5 Analog Modules

This section contains tables for Analog signal descriptions.

Table 58. ADC0 Signal Descriptions

SoC Signal Name	Module Signal Name	Description	I/O
ADC0_DM0	DADM0	ADC Channel 0 Differential Input Negative	I
ADC0_DP0	DADP0	ADC Channel 0 Differential Input Positive	I
ADC0_SE[5:1]	AD[5:1]	ADC Channel 0 Single- ended Input n	I
VREFH	V _{REFSH}	Voltage Reference Select High	I
VDDA	V_{DDA}	Analog Power Supply	I
VSSA	V _{SSA}	Analog Ground	I

Table 59. CMP0 Signal Descriptions

SoC Signal Name	Module Signal Name	Description	I/O
CMP0_IN[5:0]	IN[5:0]	Analog voltage inputs	I

Table 59. CMP0 Signal Descriptions (continued)

SoC Signal Name	Module Signal Name	Description	I/O
CMP0_OUT	CMP0	Comparator output	0

Table 60. DAC0 Signal Descriptions

SoC Signal Name	Module Signal Name	Description	I/O
DAC0_OUT	V _{OUT}	DAC output	0

Table 61. VREF Signal Descriptions

SoC Signal Name	Module Signal Name	Description	I/O
VREF_OUT		Internally generated voltage reference output	0

9.3.6 Timer Modules

This section contains tables describing timer module signals.

Table 62. TPM0 Module Signal Descriptions

SoC Signal Name	Module Signal Name	Description	I/O
TPM_CLKIN[1:0]	TPM_EXTCLK	External clock	I
TPM0_CH[3:0]	TPM_CH[3:0]	TPM channel	I/O

Table 63. TPM1 Module Signal Descriptions

SoC Signal Name	Module Signal Name	Description	I/O
TPM_CLKIN[1:0]	TPM_EXTCLK	External clock	I
TPM1_CH[1:0]	TPM_CH[1:0]	TPM channel	I/O

Table 64. TPM2 Module Signal Descriptions

SoC Signal Name	Module Signal Name	Description	I/O
TPM_CLKIN[1:0]	TPM_EXTCLK	External clock	I
TPM2_CH[1:0]	TPM_CH[1:0]	TPM channel	I/O

Table 65. LPTMR0 Module Signal Descriptions

SoC Signal Name	Module Signal Name	Description	I/O
LPTMR0_ALT[2:1]	LPTMR0_ALT[2:1]	Pulse counter input pin	

Table 66. RTC Module Signal Descriptions

SoC Signal Name	Module Signal Name	Description	I/O
RTC_CLKOUT	RTC_CLKOUT	1 Hz square-wave output	0

9.3.7 Communication Interfaces

This section contains tables for the signal descriptions for the communication modules.

Table 67. SPI0 Module Signal Descriptions

SoC Signal Name	Module Signal Name	Description	I/O
SPI0_PCS0	PCS0/SS	Chip Select/Slave Select	I/O
SPI0_PCS[2:1]	PCS[2:1]	Chip Select	0
SPI0_SCK	SCK	Serial Clock	I/O
SPI0_SIN	SIN	Data In	I
SPI0_SOUT	SOUT	Data Out	0

Table 68. SPI1 Module Signal Descriptions

SoC Signal Name	Module Signal Name	Description	I/O
SPI1_PCS0	SPI1_PCS0	Chip Select/Slave Select	I/O
SPI1_SCK	SCK	Serial Clock	I/O
SPI1_SIN	SIN	Data In	I
SPI1_SOUT	SOUT	Data Out	0

Table 69. I2C0 Module Signal Descriptions

SoC Signal Name	Module Signal Name	Description	I/O
I2C0_SCL	SCL	I2C serial clock line	I/O
I2C0_SDA	SDA	I2C serial data line	I/O

Table 70. I2C1 Module Signal Descriptions

SoC Signal Name	Module Signal Name	Description	I/O
I2C1_SCL	SCL	I2C serial clock line	I/O
I2C1_SDA	SDA	I2C serial data line	I/O

Table 71. LPUART0 Module Signal Descriptions

SoC Signal Name	Module Signal Name	Description	I/O
LPUART0_CTS_b	LPUART CTS	Clear To Send	I
LPUART0_RTS_b	LPUART RTS	Request To Send	0
LPUART0_RX	LPUART RxD	Receive Data	I
LPUART0_TX	LPUART TxD	Transmit Data ¹	I/O

^{1.} This pin is normally an output, but is an input (tristated) in single wire mode whenever the transmitter is disabled or transmit direction is configured for receive data

9.3.8 Human-Machine Interfaces(HMI)

This section contains tables describing the HMI signals.

Table 72. GPIO Module Signal Descriptions

SoC Signal Name	Module Signal Name	Description	I/O
PTA[19:16][2:0]	PORTA19-16, 2-0	General Purpose Input/ Output	I/O
PTB[18:16][3:0]	PORTB18-16, 3-0	General Purpose Input/ Output	I/O
PTC[19:16][7:1]	PORTC19-16, 7-1	General Purpose Input/ Output	1/0

Table 73. TSI0 Module Signal Descriptions

SoC Signal Name	Module Signal Name	Description	I/O
TSI0_CH[15:0]	TSI[15:0]	Touch Sensing Input capacitive pins	I/O

10 Package Information

10.1 Obtaining package dimensions

Package dimensions are provided in package drawings.

To find a package drawing, go to **nxp.com** and perform a keyword search for the drawing's document number:

Table 74. Packaging Dimensions

If you want the drawing for this package	Then use this document number
48-pin Laminate QFN (7x7)	98ASA00694D

11 Revision History

Table 75. MKW41Z Revision History

Rev. No.	Date	Substantial Changes
Rev 1	10/2016	Initial Release

How to Reach Us:

Home Page:

nxp.com

Web Support:

nxp.com/support

Information in this document is provided solely to enable system and software implementers to use NXP products. There are no express or implied copyright licenses granted hereunder to design or fabricate any integrated circuits based on the information in this document. NXP reserves the right to make changes without further notice to any products herein.

NXP makes no warranty, representation, or guarantee regarding the suitability of its products for any particular purpose, nor does NXP assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential or incidental damages. "Typical" parameters that may be provided in NXP data sheets and/or specifications can and do vary in different applications, and actual performance may vary over time. All operating parameters, including "typicals" must be validated for each customer application by customer, \(\bar{A}\)os technical experts. NXP does not convey any license under its patent rights nor the rights of others. NXP sells products pursuant to standard terms and conditions of sale, which can be found at the following address: nxp.com/SalesTermsandConditions.

Freescale and the Freescale logo are trademarks of Freescale Semiconductor, Inc., Reg. U.S. Pat. & Tm. Off. All other product or service names are the property of their respective owners. ARM, ARM Powered, Cortex, AMBA, Thumb, and TrustZone are registered trademarks of ARM Limited (or its subsidiaries) in the EU and/or elsewhere. NEON is a trademarks of ARM Limited (or its subsidiaries) in the EU and/or elsewhere.

NXP, the NXP logo, NXP SECURE CONNECTIONS FOR A SMARTER WORLD, Freescale, the Freescale logo, and Kinetis are trademarks of NXP B.V. All other product or service names are the property of their respective owners. ARM, the ARM Powered logo, and Cortex are registered trademarks of ARM Limited (or its subsidiaries) in the EU and/or elsewhere. All rights reserved.

© 2016 NXP B.V.

